

ARM®-based 32-bit Cortex®-M4 MCU with 16 KB to 64 KB Flash, sLib, 10 timers, 1 ADC, 1 COMP, 7 communication interfaces

Features

■ Core: ARM® 32-bit Cortex®-M4 CPU

- 120 MHz maximum frequency, with a memory protection unit (MPU), single-cycle multiplication and hardware division
- DSP instructions

Memories

- 16 to 64 KB of internal Flash memory
- 4 Kbytes of system memory used as a Bootloader or as a general instruction/data memory (one-time-configured)
- sLib: configurable part of main Flash set as a library area with code executable but secured, non-readable
- 8 to 16 Kbytes of SRAM

■ Power control (PWC)

- 2.4 to 3.6 V power supply
- Power-on reset (POR), low voltage reset (LVR) and power voltage monitoring (PVM)
- Low power modes: Sleep, Deepsleep and Standby modes
- Supports 5 x 32-bit battery powered registers (BPR)

■ Clock and reset management (CRM)

- 4 to 25 MHz crystal oscillator (HEXT)
- Internal 48 MHz factory-trimmed HICK (±1% at TA=25 °C, ±2% at TA= -40 to +105 °C)
- PLL flexible 31 to 500 multiplication and 1 to 15 division factor
- 32 kHz crystal (LEXT)
- Low speed internal clock (LICK)

Analog

- 1 x 12-bit 2 MSPS A/D converter, up to 15 input channels
- Temperature sensor (V_{TS})
- Internal reference voltage (V_{INTRV})
- 1 x COMP with 5 external input channels

■ DMA: 5-channel DMA controller

■ Up to 39 fast GPIOs

- All mappable on 16 external interrupts (EXINT)
- Almost all 5 V-tolerant

Up to 10 timers (TMR)

- 1 x 16-bit 7-channel advanced timer, 6channel PWM output with dead-time generator and emergency brake
- Up to 5 x 16-bit timers, each with 4 IC/OC /PWM or pulse counter and quadrature (incremental) encoder input
- 1 x 16-bit basic timer
- 2 x watchdog timers (general WDT and windowed WWDT)
- SysTick timer: a 24-bit downcounter

■ ERTC: enhanced RTC, with alarm, subsecond accuracy, hardware calendar and calibration

■ Up to 7 communication interfaces

- 2 x I²C interfaces (SMBus/PMBus)
- 2 x USARTs supporting master synchronous SPI and modem control, with ISO7816 interface, LIN, IrDA capability and swappable TX/RX
- 2 x SPIs (36 Mbit/s), all with I²S interface multiplexed
- Infrared transmitter (IRTMR)

■ CRC calculation unit

- 96-bit unique ID (UID)
- Serial wire debug (SWD) interface
- Operating temperature: -40 to +105 °C

Packages

- LQFP48 7 x 7 mm
- LQFP32 7 x 7 mm
- QFN32 5 x 5 mm
- QFN32 4 x 4 mm
- QFN28 4 x 4 mm
- TSSOP20 6.5 x 4.4 mm

Table 1. Device summary

Internal Flash	Part number
64 Kbytes	AT32F421C8T7, AT32F421K8T7, AT32F421K8U7, AT32F421K8U7-4, AT32F421G8U7, AT32F421F8P7
32 Kbytes	AT32F421C6T7, AT32F421K6T7, AT32F421K6U7, AT32F421K6U7-4, AT32F421G6U7, AT32F421F6P7
16 Kbytes	AT32F421C4T7, AT32F421K4T7, AT32F421K4U7, AT32F421K4U7-4, AT32F421G4U7, AT32F421F4P7



Contents

1	Desc	Descriptions								
2	Fund	ctional overview	11							
	2.1	ARM®Cortex®-M4	11							
	2.2	Memory	11							
		2.2.1 Internal Flash memory	11							
		2.2.2 Memory protection unit (MPU)	12							
		2.2.3 Embedded SRAM	12							
	2.3	Interrupts	12							
		2.3.1 Nested vectored interrupt controller (NVIC)	12							
		2.3.2 External interrupts (EXINT)	12							
	2.4	Power control (PWC)	12							
		2.4.1 Power supply schemes	12							
		2.4.2 Reset and power voltage monitoring (POR / LVR / PVM)	13							
		2.4.3 Voltage regulator (LDO)	13							
		2.4.4 Low-power modes	13							
	2.5	Boot modes	14							
	2.6	Clock	14							
	2.7	General-purpose inputs/outputs (GPIO)	14							
	2.8	Direct Memory Access Controller (DMA)	14							
	2.9	Timers (TMR)	15							
		2.9.1 Advanced timer (TMR1)	15							
		2.9.2 General-purpose timers (TMR3, TMR14, TMR15, TMR16 and TMR17)	16							
		2.9.3 Basic timer (TMR6)	16							
		2.9.4 SysTick timer	16							
	2.10	Watchdog (WDT)	17							
	2.11	Window watchdog (WWDT)	17							
	2.12	Enhanced real-time clock (ERTC) and battery powered registers (BPR)	17							
	2.13	Communication interfaces	17							
		2.13.1 Serial peripheral interface (SPI)								
		2.13.2 Inter-integrated sound interface (I ² S)								
		2.13.3 Universal synchronous / asynchronous receiver transmitters (USART)								

AT32F421 Series Datasheet

		2.13.4	Inter-integrated-circuit interface (I ² C)	18
		2.13.5	Infrared transmitter (IRTMR)	18
	2.14	Cyclic	redundancy check (CRC) calculation unit	18
	2.15	Analog	g-to-digital converter (ADC)	19
		2.15.1	Temperature sensor (V _{TS})	19
		2.15.2	Internal reference voltage (V _{INTRV})	19
	2.16	Compa	arator (COMP)	19
	2.17	Serial	wire debug (SWD)	19
3	Pin f	unctio	nal definitions	20
4	Mem	ory ma	apping	25
5	Elec	trical c	characteristics	26
	5.1	Param	neter conditions	26
		5.1.1	Minimum and maximum values	26
		5.1.2	Typical values	26
		5.1.3	Typical curves	26
		5.1.4	Power supply scheme	26
	5.2	Absolu	ute maximum values	27
		5.2.1	Ratings	27
		5.2.2	Electrical sensitivity	28
	5.3	Specif	ication	29
		5.3.1	General operating conditions	29
		5.3.2	Operating conditions at power-up/power-down	29
		5.3.3	Embedded reset and power control block characteristics	29
		5.3.4	Memory characteristics	31
		5.3.5	Supply current characteristics	31
		5.3.6	External clock source characteristics	39
		5.3.7	Internal clock source characteristics	43
		5.3.8	PLL characteristics	44
		5.3.9	Wakeup time from low-power mode	44
			EMC characteristics	
			GPIO port characteristics	
		5.3.12	NRST pin characteristics	47

AT32F421 Series Datasheet

		5.3.13 TMR timer characteristics	47
		5.3.14 SPI / I ² S characteristics	48
		5.3.15 I ² C interface characteristics	51
		5.3.16 12-bit ADC characteristics	52
		5.3.17 Internal reference voltage (V _{INTRV}) characteristics	55
		5.3.18 Temperature sensor (V _{TS}) characteristics	55
		5.3.19 Comparator (CMP) characteristics	56
6	Pac	kage information	58
	6.1	LQFP48 – 7 x 7 mm	58
	6.2	LQFP32 – 7 x 7 mm	60
	6.3	QFN32 – 5 x 5 mm	62
	6.4	QFN32 – 4 x 4 mm	64
	6.5	QFN28 – 4 x 4 mm	66
	6.6	TSSOP20 – 6.5 x 4.4 mm	68
	6.7	Device marking	70
	6.8	Thermal characteristics	71
7	Part	t numbering	72
Q	Doc	cument revision history	72



List of tables

Table 1. Device summary	1
Table 2. AT32F421 features and peripheral counts	10
Table 3. Bootloader supporting part numbers and pin configurations	14
Table 4. Timer feature comparison	15
Table 5. AT32F421 series pin definitions	22
Table 6. Voltage characteristics	27
Table 7. Current characteristics	27
Table 8. Temperature characteristics	27
Table 9. ESD values	28
Table 10. Latch-up values	28
Table 11. General operating conditions	29
Table 12. Operating conditions at power-up/power-down	29
Table 13. Embedded reset and power control block characteristics	29
Table 14. Programmable voltage regulator characteristics	30
Table 15. Internal Flash memory characteristics	31
Table 16. Internal Flash memory endurance and data retention	31
Table 17. Typical current consumption in Run mode	32
Table 18. Typical current consumption in Sleep mode	33
Table 19. Maximum current consumption in Run mode	34
Table 20. Maximum current consumption in Sleep mode	35
Table 21. Typical and maximum current consumption in Deepsleep and Standby modes	35
Table 22. Peripheral current consumption	38
Table 23. HEXT 4 ~ 25 MHz crystal characteristics (1)(2)	39
Table 24. HEXT external source characteristics	40
Table 25. LEXT 32.768 kHz crystal characteristics ⁽¹⁾⁽²⁾	41
Table 26. LEXT external source characteristics	42
Table 27. HICK clock characteristics	43
Table 28. LICK clock characteristics	43
Table 29. PLL characteristics	44
Table 30. Low-power mode wakeup time	44
Table 31. EMS characteristics	44
Table 32. GPIO static characteristics	45
Table 33. Output voltage characteristics	46
Table 34. Input AC characteristics	46



AT32F421 Series Datasheet

Table 35. NRST pin characteristics	47
Table 36. TMR characteristics	47
Table 37. SPI characteristics	48
Table 38. I ² S characteristics	50
Table 39. ADC characteristics	52
Table 40. R _{AIN} max for f _{ADC} = 14 MHz ⁽¹⁾	53
Table 41. R _{AIN} max for f _{ADC} = 28 MHz ⁽¹⁾	53
Table 42. ADC accuracy ⁽¹⁾	54
Table 43. Internal reference voltage characteristics	55
Table 44. Temperature sensor characteristics	55
Table 45. Comparator characteristics	56
Table 46. LQFP48 – 7 x 7 mm 48 pin low-profile quad flat package mechanical data	59
Table 47. LQFP32 – 7 x 7 mm 32 pin low-profile quad flat package mechanical data	61
Table 48. QFN32 – 5 x 5 mm 32 pin quad flat no-leads package mechanical data	63
Table 49. QFN32 – 4 x 4 mm 32 pin quad flat no-leads package mechanical data	65
Table 50. QFN28 – 4 x 4 mm 28 pin quad flat no-leads package mechanical data	67
Table 51. TSSOP20 – 6.5 x 4.4 mm 20 pin thin shrink small outline package mechanical data	69
Table 52. Package thermal characteristics	71
Table 53. AT32F421 series part numbering	72
Table 54. Decument revision history	72



List of figures

Figure 1. AT32F421 block diagram	11
Figure 2. AT32F421 LQFP48 pinout	20
Figure 3. AT32F421 LQFP32 pinout	20
Figure 4. AT32F421 QFN32 pinout	21
Figure 5. AT32F421 QFN28 pinout	21
Figure 6. AT32F421 TSSOP20 pinout	22
Figure 7. Memory map	25
Figure 8. Power supply scheme	26
Figure 9. Power-on reset and low voltage reset waveform	30
Figure 10. Typical current consumption in Deepsleep mode with LDO in Run mode vs. temperat at different V _{DD}	
Figure 11. Typical current consumption in Deepsleep mode with LDO in low-power mode vs. temperature at different V _{DD}	36
Figure 12. Typical current consumption in Standby mode vs. temperature at different V_{DD}	37
Figure 13. HEXT typical application with an 8 MHz crystal	39
Figure 14. HEXT external source AC timing diagram	40
Figure 15. LEXT typical application with a 32.768 kHz crystal	41
Figure 16. LEXT external source AC timing diagram	42
Figure 17. HICK clock accuracy vs. temperature	43
Figure 18. Recommended NRST pin protection	47
Figure 19. SPI timing diagram – slave mode and CPHA = 0	49
Figure 20. SPI timing diagram – slave mode and CPHA = 1	49
Figure 21. SPI timing diagram – master mode	49
Figure 22. I ² S slave timing diagram (Philips protocol)	50
Figure 23. I ² S master timing diagram (Philips protocol)	51
Figure 24. ADC accuracy characteristics	54
Figure 25. Typical connection diagram using the ADC	55
Figure 26. V _{TS} vs. temperature (ideal curve)	56
Figure 27. Comparator hysteresis	57
Figure 28. LQFP48 – 7 x 7 mm 48 pin low-profile quad flat package outline	58
Figure 29. LQFP32 – 7 x 7 mm 32 pin low-profile quad flat package outline	60
Figure 30. QFN32 – 5 x 5 mm 32 pin quad flat no-leads package outline	62
Figure 31. QFN32 – 4 x 4 mm 32 pin quad flat no-leads package outline	64



AT32F421 Series Datasheet

Figure 32. QFN28 – 4 x 4 mm 28 pin quad flat no-leads package outline	66
Figure 33. TSSOP20 – 6.5 x 4.4 mm 20 pin thin shrink small outline package	68
Figure 34. Marking example	70



1 Descriptions

The AT32F421 is based on the high-performance ARM®Cortex®-M4 32-bit RISC core running up to 120 MHz. The Cortex®-M4 core features a full set of DSP instructions and a memory protection unit (MPU).

The AT32F421 incorporates high-speed embedded memories (up to 64 Kbytes of internal Flash memory and 16 Kbytes of SRAM), enhanced GPIOs and peripherals connected to two APB buses. Any block of the embedded Flash memory can be protected by the "sLib", functioning as a security area with code-executable only.

The AT32F421 offers one 12-bit ADC, one analog comparator, five general-purpose 16-bit timers and one advanced timer for motor control, as well as standard and advanced communication interfaces: up to two I²C interfaces, two SPIs (all multiplexed as I²S), two USARTs and one infrared transmitter.

The AT32F421 operates in the -40 to +105 °C temperature range, from a 2.4 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power application.

The AT32F421 offers devices in different package types. Depending on the different packages, the pin-to-pin is completely compatible among devices, and also the software and functionality. Only different sets of peripherals are included.





Table 2. AT32F421 features and peripheral counts

Dart number		AT3	2F421	xxP7	AT32F421xxU7			AT32							2F421	xxT7	AT32F421xxT7		
	Part number		F6	F8	G4	G6	G8	K4	K6	K8	K4	K6	K8	K4	K6	K8	C4	C6	C8
CI	PU frequency (MHz)		120																
	Flash (Kbytes)	16	32	64	16	32	64	16	32	64	16	32	64	16	32	64	16	32	64
	SRAM (Kbytes)	8	16	16	8	16	16	8	16	16	8	16	16	8	16	16	8	16	16
	Advanced		1			1			1			1			1			1	
	16-bit general- purpose		5			5			5			5			5			5	
ร	Basic		1			1			1			1			1			1	
Timers	SysTick		1			1			1			1			1			1	
	WDT		1			1			1			1			1		1		
	WWDT		1		1			1			1			1			1		
	ERTC		1		1			1			1			1			1		
ر	I ² C		2		2			2			2			2			2		
atio	SPI	SPI 1 ⁽¹⁾					2			2			2			2			
Communication	SPI/I ² S		1 ⁽¹⁾		2			2			2			2			2		
omn	USART+UART		1+1(2)		2+0			2+0			2+0			2+0			2+0		
O	IR		1		1			1			1			1			1		
g	12-bit ADC numbers/	1				1		1			1			1			1		
Analog	channels		9			10			11		11			10			15		
4	Comparator		1			1			1		1			1			1		
	GPIO		15		23			27			27			25			39		
Op	Operating temperature		-40 °C to +105 °C																
	Package		SSOP: x 4.4			QFN28 x 4 m			QFN32 x 4 m			QFN32 x 5 m			QFP3 x 7 m			QFP4 x 7 m	

⁽¹⁾ Only SPI1/I²S1 exists on TSSOP20.
(2) All pins of USART2 are available on TSSOP20 package. USART1 only has TX and RX pins and is used as UART.



2 Functional overview

2.1 ARM®Cortex®-M4

The ARM®Cortex®-M4 processor is the latest generation of ARM® processors for embedded systems. It is a 32-bit RISC processor featuring exceptional code efficiency, outstanding computational performance and advanced response to interrupts. The processor supports a set of DSP instructions which enable efficient signal processing and complex algorithm execution. *Figure* 1 shows the general block diagram of the AT32F421.

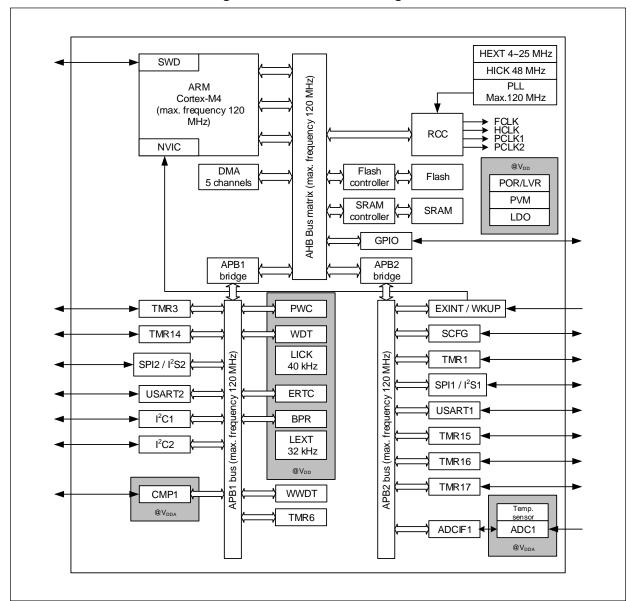


Figure 1. AT32F421 block diagram

2.2 Memory

2.2.1 Internal Flash memory

Up to 64 Kbytes of embedded Flash is available for storing programs and data. Users can configure any part of the embedded Flash memory protected by the sLib, functioning as a security area with code-executable only but non-readable. "sLib" is a mechanism that protects the intelligence of

2022.6.6 11 Ver 2.01



solution venders and facilitates the second-level development by customers.

The AT32F421 series embeds 4 Kbytes of boot code memory, in which the Bootloader is resided.

A User System Data block is included, which is used as configuration of the hardware behaviors such as read/erase/write protection and watchdog self-enable. User System Data allows to set erase/write and read protection individually, in which access protection contains two levels.

2.2.2 Memory protection unit (MPU)

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area consists of up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory. The MPU is especially suited to the applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system).

2.2.3 Embedded SRAM

Up to 16 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

2.3 Interrupts

2.3.1 Nested vectored interrupt controller (NVIC)

The AT32F421 embeds a nested vectored interrupt controller able to manage 16 priority levels and handle maskable interrupt channels plus the 16 interrupt lines of the Cortex®-M4. This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.3.2 External interrupts (EXINT)

The external interrupt (EXINT), which is connected directly with NVIC, consists of 20 edge detector lines used to generate interrupt requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The external interrupt lines connects up to 16 GPIOs.

2.4 Power control (PWC)

2.4.1 Power supply schemes

- $V_{DD} = 2.4 \sim 3.6 \text{ V}$: used as a power supply for GPIOs, ERTC, external 32 kHz crystal (LEXT), battery powered register (BPR) and the internal block such as regulator (LDO) through V_{DD} pins.
- $V_{DDA} = 2.4 \sim 3.6 \text{ V}$: used as a power supply for ADC and CMP through V_{DDA} pin. V_{DDA} and V_{SSA} must be the same voltage potential as V_{DD} and V_{SS} , respectively.



2.4.2 Reset and power voltage monitoring (POR / LVR / PVM)

The device has an integrated power-on reset (POR)/low voltage reset (PDR) circuitry. It is always active, and allows proper operation starting from/down to 2.4 V. The device remains in reset mode when V_{DD} is below a specified threshold (V_{LVR}) without the need for an external reset circuit.

The device embeds a power voltage monitor (PVM) that monitors the V_{DD} power supply and compares it to the V_{PVM} threshold. An interrupt is generated when V_{DD} drops below the V_{PVM} threshold and/or when V_{DD} rises above the V_{PVM} threshold. The PVM is enabled by software.

2.4.3 Voltage regulator (LDO)

The LDO has three operation modes: normal, low-power, and power down.

- Normal mode is used in Run/Sleep mode and in the Deepsleep mode.
- Low-power mode can be used in the Deepsleep mode.
- Power down mode is used in Standby mode: The LDO output is in high impedance and the kernel circuitry is powered down but the contents of the registers and SRAM are lost.

The LDO operates always in its normal mode after reset.

2.4.4 Low-power modes

The AT32F421 supports three low-power modes:

• Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

• **Deepsleep** mode

Deepsleep mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the LDO domain are stopped, disabling the PLL, the HICK clock, and the HEXT crystal. The voltage regulator can also be put in normal or low-power mode. The device can be woken up from Deepsleep mode by any of the EXINT line. The EXINT line source can be one of the 16 external lines, the PVM output, the ERTC alarm/tamper detection/time stamp, or the CMP wakeup.

• Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire LDO domain is powered off. The PLL, the HICK clock and the HEXT crystal are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the BPR domain and ERTC domain. The device exits Standby mode when an external reset (NRST pin), a WDT reset, a rising edge on the WKUP pin, or an ERTC alarm /tamper detection/time stamp occurs.

Note: The corresponding clock sources of ERTC and WDT are not stopped by entering Deepsleep or Standby mode.

2022.6.6 13 Ver 2.01



2.5 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from user Flash memory;
- Boot from boot code area;
- Boot from embedded SRAM.

The bootloader is stored in boot code area. It is used to reprogram the Flash memory through USART1 or USART2. *Table 3* provides the supporting interfaces of the Bootloader regarding AT32F421 part numbers and pin configurations.

Table 3. Bootloader supporting part numbers and pin configurations

Interfaces	Pins
USART1	PA9: USART1_TX
USARTI	PA10: USART1_RX
USART2	PA2: USART2_TX
USARTZ	PA3: USART2_RX

2.6 Clock

The internal 48 MHz clock (HICK) through a divided-by-6 divider (8 MHz) is selected as default CPU clock after any reset. An external 4 to 25 MHz clock (HEXT) can be selected, in which case it is monitored for failure. If failure is detected, HEXT will be switched off and the system automatically switches back to the internal HICK. A software interrupt is generated. Similarly, the system take the same action once HEXT fails when it is used as the source of PLL.

Several prescalers are used for the configuration of the AHB and the APB (APB1 and APB2) frequency. The maximum frequency of the AHB domain is 120 MHz.

2.7 General-purpose inputs/outputs (GPIO)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down), or as multiple function. Most of the GPIO pins are shared with digital or analog multiple functions. All GPIOs are high current-capable.

The GPIO's configuration can be locked, if needed, in order to avoid spurious writing to the GPIO's registers by following a specific sequence.

2.8 Direct Memory Access Controller (DMA)

The flexible 5-channel general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory, and memory-to-peripheral transfers.

The DMA controller supports circular buffer management, without the need of the intervention of user code when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and the number of transfers between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²S, I²C, USART, all timers TMRx (except TMR14) and ADC.



2.9 Timers (TMR)

The AT32F421 devices include one advanced timer, up to five general-purpose timers, one basic timer and a SysTick timer.

The table below compares the features of the advanced, general-purpose, and basic timers.

Table 4. Timer feature comparison Prescaler **DMA** request Capture/compare Complementary Counter Counter Timer type **Timer** generation resolution type factor channels outputs Any integer Up, down, 3 Advanced TMR1 16-bit between 1 4 Yes up/down and 65536 Any integer Up, down, TMR3 16-bit No between 1 Yes 4 up/down and 65536 Any integer Up, down, TMR14 16-bit 1 No between 1 No up/down Generaland 65536 purpose Any integer TMR15 16-bit 2 Up between 1 Yes 1 and 65536 Any integer TMR16 16-bit Up between 1 Yes 1 1 TMR17 and 65536 Any integer Basic TMR6 16-bit Up between 1 Yes No No

2.9.1 Advanced timer (TMR1)

The advanced timer (TMR1) can be seen as a three-phase PWM multiplexed assigned to 6 channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be used as a complete general-purpose timer. These four independent channels can be used for:

and 65536

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes)
- One-cycle mode output

If configured as a standard 16-bit timer, it has the same features as the TMRx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0-100%).

In debug mode, the advanced timer counter can be frozen and the PWM outputs disabled to turn off any power switch driven by these outputs.

Many features are shared with those of the general-purpose TMR which have the same architecture. The advanced timer can therefore work together with the TMR timers via the link feature for synchronization or event chaining.



2.9.2 General-purpose timers (TMR3, TMR14, TMR15, TMR16 and TMR17)

There are 5 synchronizable general-purpose timers embedded in the AT32F421.

TMR3

The TMR3 timer is based on a 16- bit auto-reload upcounter/downcounter and a 16-bit prescaler. They can offer four independent channels on the largest package. Each channel can be used for input capture/output compare, PWM or one-cycle mode output.

It can work together with the advanced timers via the link feature for synchronization or event chaining. In debug mode, the counter can be frozen. TMR3 can be used to generate PWM outputs. It has an individual DMA request mechanism.

This timer TMR3 is also capable of handling incremental encoder signals and the digital outputs coming from 1 to 3 hall-effect sensors.

TMR14

The TMR14 timer is based on a 16-bit auto-reload upcounter, a 16-bit prescaler, and one independent channels for input capture/output compare, PWM, or one-cycle mode output. It can not only be synchronized with full-featured general-purpose timers, and but also can be used as simple time bases.

• TMR15, TMR16 and TMR17

These three timers are based on a 16-bit auto-reload upcounter, a 16-bit prescaler. TMR15 features two channels and one complementary channel. TMR16 and TMR17 have one channel and one complementary channel, respectively. All channels can be used for input capture/output compare, PWM, or one-pulse mode output.

They can work together via the Timer link feature for synchronization or event chaining. In debug mode, the counter can be frozen. These timers have independent DMA request generation.

2.9.3 Basic timer (TMR6)

This timer is used as a generic 16-bit time base.

2.9.4 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features include:

- A 24-bit downcounter
- Auto reload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source



2.10 Watchdog (WDT)

The watchdog consists of a 12-bit downcounter and 8-bit prescaler. It is clocked by an independent internal LICK clock. As it operates independently from the main clock, it can operate in Deepsleep and Standby modes. It can be used either as a watchdog to reset the device when an error occurs, or as a free running timer for application timeout management. It is self-enabling or not through the User System Data configuration. The counter can be frozen in debug mode.

2.11 Window watchdog (WWDT)

The window watchdog embeds a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

2.12 Enhanced real-time clock (ERTC) and battery powered registers (BPR)

The battery powered domain includes:

- Enhanced real-time clock (ERTC)
- Five 32-bit battery powered registers

The enhanced real-time clock (ERTC) is an independent BCD timer/counter. It supports the following features:

- Calendar with second, minute, hour (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- The sub-seconds value is also available in binary format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Programmable alarms with wake up from Stop or Standby mode capability
- Digital calibration circuit with 1 ppm resolution, to compensate quartz crystal inaccuracy.

The alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. Other 32-bit registers also contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The battery powered registers are 32-bit registers used to store 20 bytes of user application data. Battery powered registers are not reset by a system, or when the device wakes up from the Standby mode.

2.13 Communication interfaces

2.13.1 Serial peripheral interface (SPI)

Two SPIs are able to communicate up to 36 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC/SDHC modes. Both SPIs can be served by the DMA controller.



2.13.2 Inter-integrated sound interface (I²S)

Two standard I²S interfaces (multiplexed with SPI) are available, that can be operated in master or slave mode. These interfaces can be configured to operate with 16/24/32 bit resolution, as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When any of the I²S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency. Both I²S can be served by the DMA controller.

2.13.3 Universal synchronous / asynchronous receiver transmitters (USART)

The AT32F421 embeds two universal synchronous/asynchronous receivers/transmitters (USART1 and USART2).

These two USART interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, master synchronous communication, single-wire half-duplex communication mode, and have LIN Master/Slave capability. These two USART interfaces also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant). These two USART interfaces can be served by the DMA controller. TX/RX pins are swappable configuration.

Two USARTs are able to communicate at speeds of up to 7.5 Mbit/s.

2.13.4 Inter-integrated-circuit interface (I²C)

Two I²C bus interfaces can operate in multi-master and slave modes. They can support standard (up to 100 Kbit/s) and fast modes (up to 400 Kbit/s). The I²C bus frequency can be increased up to 1 MHz. For more details, please contact your nearest Artery sales office for technical support.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is included.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.13.5 Infrared transmitter (IRTMR)

The AT32F421 device provides an infrared transmitter solution. The solution is based on the internal connection between TMR16, USART1 or USART2 and TMR17. TMR17 is used to provide the carrier frequency, and TMR16, USART1 or USART2 provides the main signal to be sent. The infrared output signal is available on PB9 or PA13.

To generate infrared remote control signals, TMR16 channel 1 and TMR17 channel 1 must be correctly configured to generate the correct waveform. All standard IR pulse modulation modes can be obtained by programming two timer output compare channels.

2.14 Cyclic redundancy check (CRC) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial. Among other applications, CRC-based techniques are used to verify data transmission or storage integrity.



2.15 Analog-to-digital converter (ADC)

One 12-bit analog-to-digital converter is embedded into AT32F421 devices and it has up to 15 external channels and 3 internal channels (temperature sensor V_{TS} , internal reference voltage V_{REFINT} , and V_{SSA}). In sequence mode, automatic conversion is performed on a selected group of analog inputs. The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TMRx) and the advanced timer (TMR1) can be internally connected to the ADC start trigger and injection trigger, respectively, to allow the application to synchronize ADC conversion and timers.

2.15.1 Temperature sensor (V_{TS})

The temperature sensor has to generate a voltage V_{TS} that varies linearly with temperature. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The offset of this line varies from chip to chip due to process variation. The internal temperature sensor is more suited to applications that detect temperature variations instead of absolute temperatures. If accurate temperature readings are needed, an external temperature sensor part should be used.

2.15.2 Internal reference voltage (VINTRV)

The internal reference voltage (V_{INTRV}) provides a stable voltage source for ADC. The V_{INTRV} is internally connected to the ADC1_IN17 input channel.

2.16 Comparator (COMP)

The AT32F421 embeds one rail-to-rail comparator with programmable reference voltage (internal or external), hysteresis, speed, selectable output polarity, output blanking and noise filter.

The reference voltage can be one of the following:

- External GPIO
- Internal reference voltage (V_{INTRV}) or submultiple (1/4, 1/2, 3/4)

The comparator can wake up from Deepsleep mode, and also can generate interrupts and breaks for timers.

2.17 Serial wire debug (SWD)

The ARM® SWD interface is embedded, and is a serial wire debug port that enables a serial wire debug to be connected to the target to implement the programming and debugging of the target.



3 Pin functional definitions

Figure 2. AT32F421 LQFP48 pinout

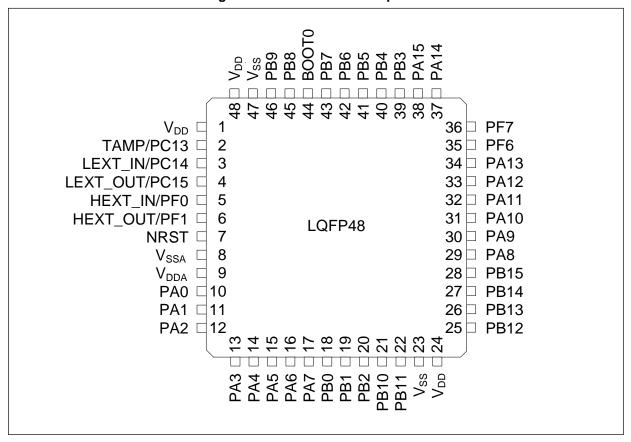


Figure 3. AT32F421 LQFP32 pinout

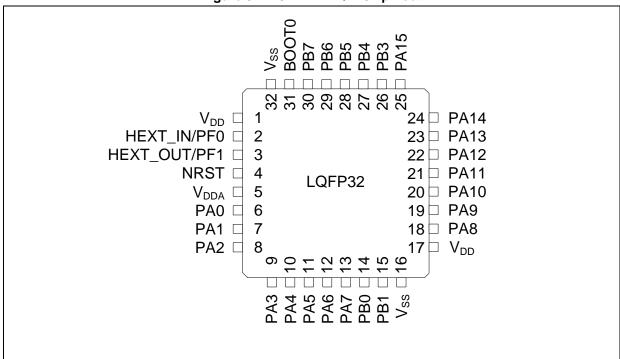




Figure 4. AT32F421 QFN32 pinout

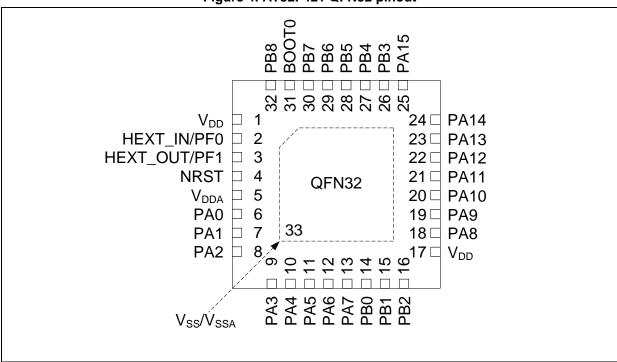
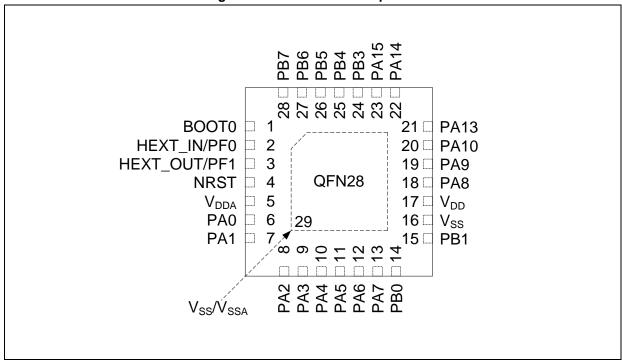


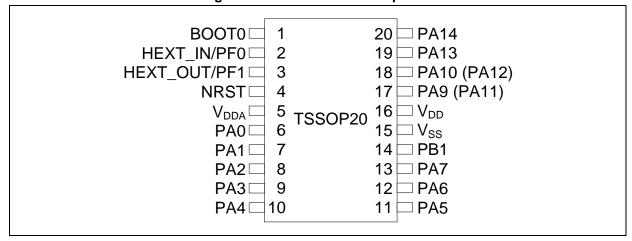
Figure 5. AT32F421 QFN28 pinout



2022.6.6 21 Ver 2.01



Figure 6. AT32F421 TSSOP20 pinout



The table below is the pin definition of the AT32F421. "-" presents there is no such pinout on the related package. Unless otherwise specified, the pins during and after reset have the same functions as those of actual ones, and all GPIOs are configured as floating input during and after reset. Alternate functions of pins are enabled through the GPIOx_MUXx register, and additional functions are selected through peripheral registers.

Table 5. AT32F421 series pin definitions

	Pin number						7				
TSSOP20	QFN28	QFN32	LQFP32	LQFP48	Pin name (after reset)	Pin type ⁽¹⁾	GPIO structure ⁽²⁾	Alternate function	Additional function		
-	-	1	1	1	V_{DD}	S	-	Digital power	supply		
-	-	-	-	2	PC13	I/O	FT	-	TAMP1 / WKUP2		
-	-	•	-	3	PC14 / LEXT_IN (PC14)	I/O	тс	-	LEXT_IN		
	1	ı	1	4	PC15 / LEXT_OUT (PC15)	I/O	тс	-	LEXT_OUT		
2	2	2	2	5	PF0 / HEXT_IN (PF0)	I/O	тс	I2C1_SDA	HEXT_IN		
3	3	3	3	6	PF1 / HEXT_OUT (PF1)	I/O	тс	I2C1_SCL	HEXT_OUT		
4	4	4	4	7	NRST	I/O	R	Device reset input / internal	reset input (active low)		
-	-	1	-	8	V _{SSA} / V _{REF} -	S	-	Analog ground / negative	e reference voltage		
5	5	5	5	9	V _{DDA} / V _{REF+}	S	-	Analog power supply / posi	tive reference voltage		
6	6	6	6	10	PA0	I/O	FTa	TMR1_EXT / USART2_CTS / I2C2_SCL / CMP1_OUT	ADC1_IN0 / CMP1_INP2 / CMP1_INM6 / WKUP1		
7	7	7	7	11	PA1	I/O	FTa	TMR15_CH1C / USART2_RTS / I2C2_SDA / EVENTOUT	ADC1_IN1 / CMP1_INP1		
8	8	8	8	12	PA2	I/O	FTa	TMR15_CH1 / USART2_TX	ADC1_IN2 / CMP1_INM7		
9	9	9	9	13	PA3	I/O	FTa	TMR15_CH2 / USART2_RX / I2S2_MCK	ADC1_IN3		
10	10	10	10	14	PA4	I/O	FTa	TMR14_CH1 / USART2_CK / SPI1_CS / I2S1_WS ADC1_IN4/ CMP1_II			
11	11	11	11	15	PA5	I/O	FTa	SPI1_SCK/I2S1_CK	ADC1_IN5 / CMP1_INP0 / CMP1_INM5		

2022.6.6 22 Ver 2.01





Pin number						_	(2		
TSSOP20	QFN28	QFN32	LQFP32	LQFP48	Pin name (after reset)	Pin type ⁽¹⁾	GPIO structure ⁽²⁾	Alternate function	Additional function
12	12	12	12	16	PA6	I/O	FTa	TMR1_BRK / TMR3_CH1 / TMR16_CH1 / SPI1_MISO / I2S1_MCK / I2S2_MCK / CMP1_OUT / EVENTOUT	ADC1_IN6
13	13	13	13	17	PA7	I/O	FTa	TMR1_CH1C / TMR3_CH2 / TMR14_CH1 / TMR17_CH1 / SPI1_MOSI / I2S1_SD / EVENTOUT	ADC1_IN7
-	14	14	14	18	PB0	I/O	FTa	TMR1_CH2C / TMR3_CH3 / USART2_RX / I2S1_MCK / EVENTOUT	ADC1_IN8
14	15	15	15	19	PB1	I/O	FTa	TMR1_CH3C / TMR3_CH4 / TMR14_CH1 / SPI2_SCK / I2S2_CK	ADC1_IN9
-	1	16	1	20	PB2	I/O	FTa	TMR3_EXT	ADC1_IN10
-	-	-	-	21	PB10	I/O	FT	SPI2_SCK / I2S2_CK / I2C2_SCL	-
-	-	-	-	22	PB11	I/O	FT	I2C2_SDA / EVENTOUT	-
15	16	-	16	23	V_{SS}	S	-	Digital gro	ound
16	17	17	17	24	V_{DD}	S	-	Digital power	supply
-	-	-	-	25	PB12	I/O	FTa	TMR1_BRK / TMR15_BRK / SPI2_CS / I2S2_WS / I2C2_SMBA / EVENTOUT	ADC1_IN11
-	1	-	1	26	PB13	I/O	FTa	TMR1_CH1C / SPI2_SCK / I2S2_CK / I2C2_SCL	ADC1_IN12
-	1	-	-	27	PB14	I/O	FTa	TMR1_CH2C / TMR15_CH1 / SPI2_MISO / I2S2_MCK / I2C2_SDA	ADC1_IN13
-	-	-	-	28	PB15	I/O	FTa	TMR1_CH3C / TMR15_CH2 / TMR15_CH1C / SPI2_MOSI / I2S2_SD	ADC1_IN14 / ERTC_REFIN / WKUP7
-	18	18	18	29	PA8	I/O	FT	TMR1_CH1 / USART1_CK / UART2_TX / I2C2_SCL / CLKOUT / EVENTOUT	-
17	19	19	19	30	PA9	I/O	FT	TMR1_CH2 / TMR15_BRK / USART1_TX / I2C1_SCL / I2C2_SMBA / CLKOUT	-
18	20	20	20	31	PA10	I/O	FT	TMR1_CH3 / TMR17_BRK / USART1_RX / I2C1_SDA	-
17 ⁽³⁾	_(4)	21	21	32	PA11	I/O	FT	TMR1_CH4 / USART1_CTS / I2C1_SMBA / I2C2_SCL / CMP1_OUT / EVENTOUT	-
18(3)	_(4)	22	22	33	PA12	I/O	FT	TMR1_EXT / USART1_RTS / I2C2_SDA / EVENTOUT	-
19	21	23	23	34	PA13 (SWDIO ⁽⁵⁾)	I/O	FT	PA13 / IR_OUT / SPI2_MISO / I2S2_MCK	-
-	-	-	-	35	PF6	I/O	FT	I2C2_SCL	-
-	-	-	1	36	PF7	I/O	FT	I2C2_SDA	-



AT32F421 Series Datasheet

	Pin	num	ber			_	2)	Alternate function Additional function	
TSSOP20	QFN28	QFN32	LQFP32	LQFP48	Pin name (after reset)	Pin type ⁽¹⁾	GPIO structure ⁽²⁾		
20	22	24	24	37	PA14 (SWCLK ⁽⁵⁾)	I/O	FT	PA14 / USART2_TX / SPI2_MOSI / I2S2_SD	-
-	23	25	25	38	PA15	I/O	FT	USART2_RX / SPI1_CS / I2S1_WS / SPI2_CS / I2S2_WS / EVENTOUT	-
-	24	26	26	39	PB3	I/O	FT	SPI1_SCK / I2S1_CK / SPI2_SCK / I2S2_CK / EVENTOUT	-
-	25	27	27	40	PB4	I/O	FT	TMR3_CH1 / TMR17_BRK / SPI1_MISO / I2S1_MCK / SPI2_MISO / I2S2_MCK / I2C2_SDA / EVENTOUT	-
-	26	28	28	41	PB5	1/0	FT	TMR3_CH2 / TMR16_BRK / SPI1_MOSI / I2S1_SD / SPI2_MOSI / I2S2_SD / I2C1_SMBA	WKUP6
-	27	29	29	42	PB6	I/O	FT	TMR16_CH1C / USART1_TX / I2S1_MCK / I2C1_SCL	-
-	28	30	30	43	PB7	I/O	FT	TMR17_CH1C / USART1_RX / I2C1_SDA	-
1	1	31	31	44	BOOT0	ı	В	Boot mode se	lection 0
-	-	32	-	45	PB8	I/O	FT	TMR16_CH1 / I2C1_SCL	-
-	-	-	1	46	PB9	I/O	FT	TMR17_CH1 / IR_OUT / SPI2_CS / I2S2_WS / I2S1_MCK / I2C1_SDA / EVENTOUT	-
-	-	-	32	47	V _{SS}	S	-	Digital ground	
-	-	-	-	48	V_{DD}	S	-	Digital power supply	
-	29	33	1	-	EPAD (Vss/Vssa)	S	-	Digital ground / Analog ground	

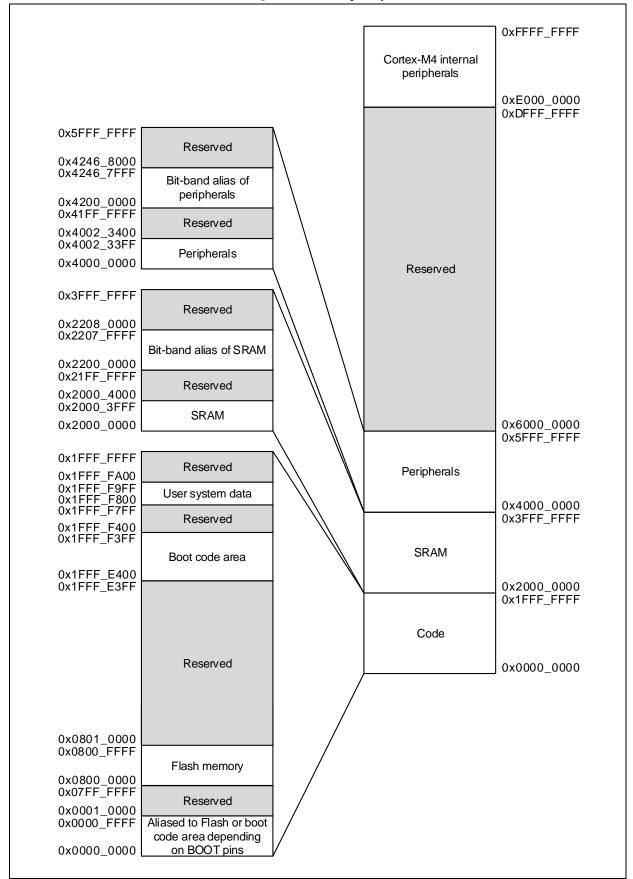
- (1) I = input, O = output, S = supply.
- (2) TC = standard level, FT = general 5 V-tolerant, FTa = 5 V-tolerant with analog functions, R = bidirectional reset pin with embedded weak pull-up resistor, B = dedicated BOOT0 pin with embedded weak pull-down resistor. FTa is a 5 V-tolerant pin when set as input floating, input pull-up, or input pull-down; when set as analog mode, it loses 5 V tolerant characteristic, and in this case, the input level must be less than VDD + 0.3 V.
- (3) For TSSOP20 package, PA11/PA12 and its alternate function can be remapped to replace the original PA9/PA10 and its alternate function by software.
- (4) For QFN28 package, PA11 and PA12 should be treated as unconnected pins (even they are not available on the package). They are not forced to a defined level by hardware. It is suggested to configure the state of these two pins as a low level output to prevent unnecessary current leakage.
- (5) After reset, PA13/PA14 pin is configured as alternate function SWDIO/SWCLK, and the internal pull-up on the SWDIO pin and the internal pull-down on the SWCLK pin are activated.

2022.6.6 24 Ver 2.01



4 Memory mapping

Figure 7. Memory map





5 Electrical characteristics

5.1 Parameter conditions

5.1.1 Minimum and maximum values

The minimum and maximum values are guaranteed in the worst conditions. Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production.

5.1.2 Typical values

Typical data are based on T_A = 25 °C, V_{DD} = 3.3 V.

5.1.3 Typical curves

All typical curves are given only as design guidelines and are not tested.

5.1.4 Power supply scheme

Backup circuitry (LEXT, ERTC, Wake-up logic, BPR registers) OUT shifter Ю Logic Level Kernel logic (CPU, Digital & Memories) LDO 2 x 100 nF 100 nF ADC, CMP RCs, PLL,

Figure 8. Power supply scheme



5.2 Absolute maximum values

5.2.1 Ratings

If stresses were out of the absolute maximum ratings listed *Table 6*, *Table 7* and *Table 8*, it may cause permanent damage to the device. These are maximum stress ratings only that the device could bear, but the functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for an extended period of times may affect device reliability.

Table 6. Voltage characteristics

Symbol	Ratings	Min	Max	Unit	
V V	External main supply voltage (including V _{DDA} and	rnal main supply voltage (including V _{DDA} and			
V_{DD} - V_{SS}	V _{DD})	-0.3	4.0	V	
	Input voltage on FT GPIO				
	Input voltage on FTa GPIO (set as input floating,	V _{SS} -0.3	6.0		
V_{IN}	input pull-up or input pull-down mode)				
	Input voltage on TC GPIO	V 0.2	4.0		
	Input voltage on FTa GPIO (set as analog mode)	V _{SS} -0.3	4.0		
$ \Delta V_{DDx} $	Variations between different V _{DD} power pins	-	50	mV	
V _{SSx} -V _{SS}	Variations between all the different ground pins	-	50	1117	

Table 7. Current characteristics

Symbol	Ratings	Max	Unit
I_{VDD}	Total current into V _{DDA} /V _{DD} power lines (source)	150	
I _{VSS}	Total current out of V _{SS} ground lines (sink)	150	mA
1	Output current sunk by any GPIO and control pin	25	IIIA
IΙΟ	Output current source by any GPIO and control pin	-25	

Table 8. Temperature characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	-60 ~ +150	°C
TJ	Maximum junction temperature	125	



5.2.2 Electrical sensitivity

Based on three different tests (HBM, CDM, and LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges are applied to the pins of each sample according to each pin combination. This test conforms to the JS-001-2017/JS-002-2018 standard.

Table 9. ESD values

Symbol	Parameter	Conditions	Class	Max ⁽¹⁾	Unit
Vesd(HBM)	Electrostatic discharge voltage (human body model)	$T_A = +25$ °C, conforms to JS-001- 2017	3A	±6000	V
Vesd(cdm)	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforms to JS-002- 2018	III	±1000	V

⁽¹⁾ Guaranteed by characterization results, not tested in production.

Static latch-up

Tests compliant with EIA/JESD78E IC latch-up standard are required to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin;
- A current injection is applied to each input, output and configurable GPIO pin.

Table 10. Latch-up values

Symbol	Parameter	Conditions	Level/Class
111		$T_A = +105$ °C, conforming to	II lovel A (+200 mA)
LU	Static latch-up	EIA/JESD78E	II level A (±200 mA)

2022.6.6 28 Ver 2.01



5.3 Specification

5.3.1 General operating conditions

Table 11. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f	Internal AHB clock		0	120	MU
fhclk	frequency	-	0	120	MHz
fpclk1/2	Internal APB1/2 clock		0	fHCLK	MHz
IPCLK1/2	frequency	-	0	IHCLK	IVITZ
V _{DD}	Standard operating voltage	-	2.4	3.6	V
V_{DDA}	Analog operating voltage	Must be the same potential as VDD	V_{DD}		V
		LQFP48 (7 x 7 mm)	-	230	
		LQFP32 (7 x 7 mm)	-	243	
Ъ	Power dissipation: T _A =	QFN32 (5 x 5 mm)	-	503	\^/
P _D	105 °C	QFN32 (4 x 4 mm)	-	446	mW
		QFN28 (4 x 4 mm)	-	446	
		TSSOP20 (6.5 x 4.4 mm)	-	194	
TA	Ambient temperature	-	-40	105	°C

5.3.2 Operating conditions at power-up/power-down

Table 12. Operating conditions at power-up/power-down

Symbol	Parameter	Conditions	Min	Max	Unit
	V _{DD} rise time rate		0	∞	ms/V
t _{VDD}	V _{DD} fall time rate	-	20	∞	μs/V

5.3.3 Embedded reset and power control block characteristics

Table 13. Embedded reset and power control block characteristics

Symbol	Parameter	Min	Тур	Max	Unit
VPOR ⁽¹⁾	Power-on reset threshold	1.73	2.06	2.4	V
V _{LVR} ⁽¹⁾	Low voltage reset threshold		1.88	2.16	V
V _{LVRhyst} ⁽¹⁾	LVR hysteresis	-	180	-	mV
Tresttempo ⁽¹⁾	Reset temporization: CPU starts execution after V _{DD} keeps	_	4.5		mo
TRESTTEMPO(**)	higher than VPOR for TRSTTEMPO		4.5	-	ms

⁽¹⁾ Guaranteed by design, not tested in production.

⁽²⁾ The product behavior is guaranteed by design down to the minimum V_{LVR} value.



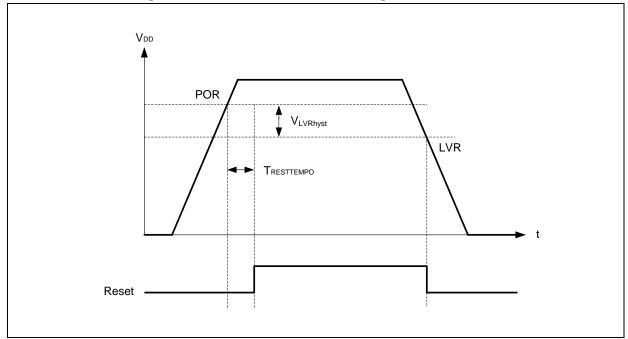


Figure 9. Power-on reset and low voltage reset waveform

Table 14. Programmable voltage regulator characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Variati	PVM threshold 1 (PVMSEL[2:0] =	Rising edge ⁽¹⁾	2.19	2.28	2.37	V
VPVM1	001)	Falling edge	2.09	2.18	2.27	V
VPVM2	PVM threshold 2 (PVMSEL[2:0] =	Rising edge (2)	2.28	2.38	2.48	V
VPVM2	010)	Falling edge (2)	2.18	2.28	2.37 2.27 2.48 2.38 2.58 2.48 2.69 2.59 2.79 2.69 2.9 2.8 3	V
\ <i>I</i>	PVM threshold 3 (PVMSEL[2:0] =	Rising edge (2)	2.38	2.48	2.58	V
VPVM3	011)	Falling edge (2)	2.28	2.38	28	V
VPVM4	PVM threshold 4 (PVMSEL[2:0] =	Rising edge (2)	2.47	2.58	2.69	V
V PVM4	100)	Falling edge (2)	2.37	2.48	2.59	V
\	PVM threshold 5 (PVMSEL[2:0] =	Rising edge (2)	2.57	2.68	2.79	V
VPVM5	101)	Falling edge (2)	2.47	2.58	2.37 2.27 2.48 2.38 2.58 2.48 2.69 2.59 2.79 2.69 2.9 2.8 3 2.9	V
VPVM6	PVM threshold 6 (PVMSEL[2:0] =	Rising edge 2)	2.66	2.78	2.9	V
VPVM6	110)	Falling edge (2)	2.56	2.68	2.37 2.27 2.48 2.38 2.58 2.48 2.69 2.59 2.79 2.69 2.9 2.8 3 2.9	V
V _{PVM7}	PVM threshold 7 (PVMSEL[2:0] =	Rising edge	2.76	2.88	3	V
VPVM7	111)	Falling edge	2.66	2.78	2.9	V
V _{HYS_P} ⁽²⁾	PVM hysteresis	-	-	100	-	mV
I _{DD} (PVM)	PVM current consumption	-	-	20	30(2)	μA

 ⁽¹⁾ PVMSEL [2:0] = 001 may not be used because it is lower than VPOR.
 (2) Guaranteed by design, not tested in production.



5.3.4 Memory characteristics

Table 15. Internal Flash memory characteristics

Symbol	Parameter	Тур	Max ⁽¹⁾	Unit
T _{PROG}	Programming time	60	65	μs
terase	Page erase time	6.6	8	ms
tME	Mass erase time	8.2	10	ms

⁽¹⁾ Guaranteed by design, not tested in production.

Table 16. Internal Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max	Unit
Nend	Endurance	T _A = -40 ~ 105 °C	100	-	-	kcycles
tret	Data retention	T _A = 105 °C	10			years

⁽¹⁾ Guaranteed by design, not tested in production.

5.3.5 Supply current characteristics

The current consumption is subjected to several parameters and factors such as the operating voltage, ambient temperature, GPIO pin loading, device software configuration, operating frequencies, GPIO pin switching rate, and executed binary code. The current consumption is obtained by characterization results, not tested in production.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All GPIO pins are in analog mode.
- Flash memory access time depends on f_{HCLK} (0 ~ 32 MHz: zero-wait state; 33 ~ 64 MHz: one-wait state; 65 ~ 96 MHz: two-wait states; over 96 MHz: three-wait states).
- Prefetch is ON.
- fpclk1 = fhclk, fpclk2 = fhclk, fadcclk = fpclk2/8.
- Unless otherwise specified, the typical values are measured with $V_{DD} = 3.3 \text{ V}$ and $T_A = 25 \text{ °C}$ condition and the maximum values are measured with $V_{DD} = 3.6 \text{ V}$.

2022.6.6 31 Ver 2.01





Table 17. Typical current consumption in Run mode

				Ty	ур		
Symbol	Parameter	Conditions	fHCLK	All peripherals enabled	All peripherals disabled	Unit	
			120 MHz	16.7	11.3		
			108 MHz	15.2	10.3		
			72 MHz	10.5	7.19	Unit mA	
			48 MHz	7.62	5.44		
			36 MHz	5.98	4.34		
		l link and automal	24 MHz	4.65	3.54		
		High-speed external crystal (HEXT) ⁽¹⁾⁽²⁾	16 MHz	3.45	2.71	mA	
			8 MHz	1.96	1.57		
			4 MHz	1.50	1.30		
			2 MHz	1.27	1.16		
			1 MHz	1.16	1.10		
			500 kHz	1.10	1.07		
,	Supply current		125 kHz	1.06	1.04		
I _{DD}	in Run mode		120 MHz	16.7	11.3	mA	
			108 MHz	15.1	10.3		
			72 MHz	10.4	7.14		
			48 MHz	7.52	5.38		
			36 MHz	5.88	4.27		
			24 MHz	4.53	3.47		
		High-speed internal clock	16 MHz	3.34	2.63	mA	
		(HICK)	8 MHz	1.83	1.48		
			4 MHz	1.37	1.20		
			2 MHz	1.15	1.06		
			1 MHz	1.03	0.99		
			500 kHz	0.97	0.95		
			125 kHz	0.93	0.93		

2022.6.6 Ver 2.01

⁽¹⁾ External clock is 8 MHz.(2) PLL is ON when f_{HCLK} > 8 MHz.



Table 18. Typical current consumption in Sleep mode

			/p				
Symbol	Parameter	Conditions	fHCLK	All peripherals enabled	All peripherals disabled	Unit	
			120 MHz	12.2	4.99		
			108 MHz	11.1	4.59	mA	
			72 MHz	7.76	3.38		
			48 MHz	5.81	2.89		
			36 MHz	4.60	2.42		
		I link and a day to made to sate	24 MHz	3.70	2.25		
		High-speed external crystal (HEXT) ⁽¹⁾⁽²⁾	16 MHz	2.80	1.83	mA	
			8 MHz	1.60	1.11		
			4 MHz	1.30	1.05		
			2 MHz	1.15	1.02		
			1 MHz	1.07	1.00		
			500 kHz	1.03	0.99		
	Supply current in Sleep mode		125 kHz	1.00	0.98		
I _{DD}			120 MHz	12.1	4.88		
			108 MHz	11.0	4.47		
			72 MHz	7.65	3.27		
			48 MHz	5.70	2.78		
			36 MHz	4.49	2.30		
			24 MHz	3.59	2.13		
	High-speed internal clock (HICK)	16 MHz	2.68	1.71	mA		
		(HICK)	8 MHz	1.47	0.98		
			4 MHz	1.17	0.93		
			2 MHz	1.02	0.89		
			1 MHz	0.94	0.88		
			500 kHz	0.90	0.87		
			125 kHz	0.87	0.86		

2022.6.6 Ver 2.01

⁽¹⁾ External clock is 8 MHz.(2) PLL is ON when f_{HCLK} > 8 MHz.



Table 19. Maximum current consumption in Run mode

0	D	O and distant		N	lax	11!1
Symbol	Parameter	Conditions	f _{HCLK}	T _A = 85 °C	T _A = 105 °C	Unit
			120 MHz	18.9	20.7	
			108 MHz	17.3	19.1	
		High-speed external crystal (HEXT) ⁽¹⁾ All peripherals enabled	72 MHz	12.6	14.4	
			48 MHz	9.69	11.5	m Λ
			36 MHz	8.04	9.81	mA
			24 MHz	6.69	8.45	mA mA
	0		16 MHz	5.49	7.24	
I _{DD}	Supply current in Run mode		8 MHz	3.99	5.73	
	iii Ruii iiiode		120 MHz	13.5	15.2	mA
			108 MHz	12.4	14.2	
	High-speed external crystal (HEXT) ⁽¹⁾	High-speed external crystal	72 MHz	9.29	11.0	
		48 MHz	7.52	9.26	mA	
		All peripherals disabled	36 MHz	6.41	8.14	
			24 MHz	5.60	7.33	
			16 MHz	4.76	6.49	

⁽¹⁾ External clock is 8 MHz, and PLL is ON when f_{HCLK} > 8 MHz.



Table 20. Maximum current consumption in Sleep mode

Symbol	D	0		N	lax	llnit	
	Parameter	Conditions	f _{HCLK}	T _A = 85 °C	T _A = 105 °C	Unit	
			120 MHz	14.4	16.1		
			108 MHz	13.3	15.0		
		High-speed external crystal (HEXT) ⁽¹⁾ All peripherals enabled	72 MHz	9.85	11.6		
			48 MHz	7.89	9.58	^	
			36 MHz	6.69	8.36	mA	
			24 MHz	5.79	7.45		
			16 MHz	4.88	6.53		
	Supply current		8 MHz	3.68	5.31		
I _{DD}	in Sleep mode		120 MHz	7.06	8.70		
		High-speed external crystal (HEXT)(1) All peripherals disabled	108 MHz	6.66	8.30		
			72 MHz	5.45	7.09		
			48 MHz	4.96	6.57	mA	
			36 MHz	4.48	6.12	IIIA	
			24 MHz	4.31	5.93		
			16 MHz	3.89	5.53		
			8 MHz	3.18	4.81		

⁽¹⁾ External clock is 8 MHz, and PLL is ON when f_{HCLK} > 8 MHz.

Table 21. Typical and maximum current consumption in Deepsleep and Standby modes

Symbol			Typ ⁽¹⁾		Max ⁽²⁾			
	Parameter	Conditions	V _{DD} = 2.4	V _{DD} =	T _A =	T _A =	T _A =	Unit
			V	3.3 V	25 °C	85 °C	105 °C	
lob	Supply current in Deepsleep mode ⁽³⁾	LDO in normal mode, HICK and HEXT OFF (no WDT)	445	450	See ⁽⁴⁾	4100	6750	- μΑ
		LDO in low-power mode, LPDS1=1, HICK and HEXT OFF (no WDT)	205	210		2000	3315	
	Supply current	LEXT and ERTC OFF	2.4	3.6	4.6	5.9	7.6	
	in Standby mode	LEXT and ERTC ON	3.2	5.1	5.9	7.2	9.2	μΑ

2022.6.6 Ver 2.01

⁽¹⁾ Typical values are measured at T_A = 25 °C.
(2) Guaranteed by characterization results, not tested in production.

⁽³⁾ Before entering Deepsleep mode, CRM_AHBEN[4] (FLASHEN) must be set to 1; otherwise, an additional 50 μA of current consumption is generated for typical values.

⁽⁴⁾ This value may be several times the typical value due to process variations.



Figure 10. Typical current consumption in Deepsleep mode with LDO in Run mode vs. temperature at different V_{DD}

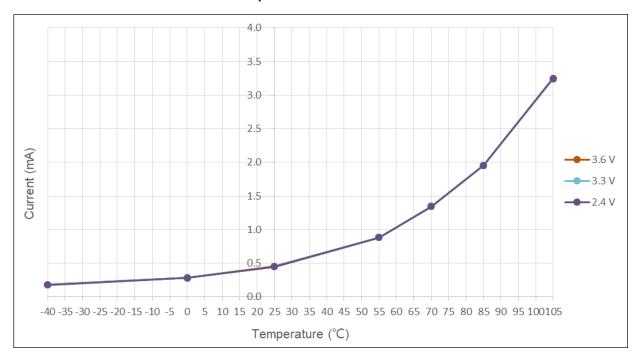


Figure 11. Typical current consumption in Deepsleep mode with LDO in low-power mode vs. temperature at different V_{DD}

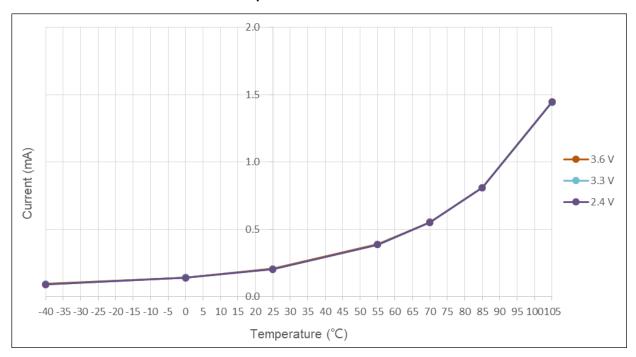
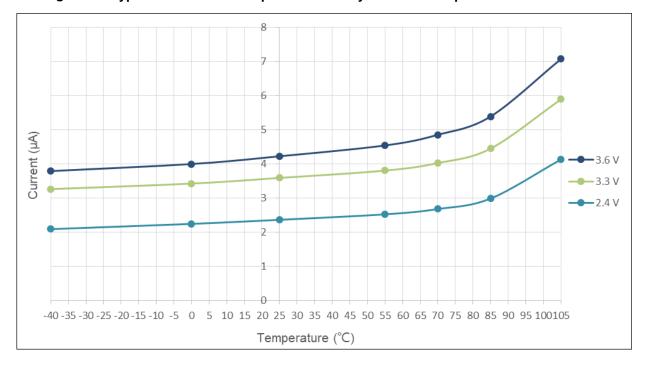




Figure 12. Typical current consumption in Standby mode vs. temperature at different V_{DD}





On-chip peripheral current consumption

The MCU is placed under the following conditions:

- All GPIO pins are in analog mode.
- The given value is calculated by measuring the current consumption difference between "all peripherals clocked OFF" and "only one peripheral clocked ON".

Table 22. Peripheral current consumption

Pe	eripheral	Тур	Unit
	DMA1	2.15	
	SRAM	1.06	
	Flash	12.08	
AHB	GPIOA	0.50	
AHB	GPIOB	0.50	
	GPIOC	0.50	
	GPIOF	0.50	
	CRC	0.70	
	TMR3	6.29	
	TMR6	0.49	
	TMR14	2.28	
	SPI2/I ² S2	2.26	
APB1	USART2	2.11	μA/MHz
	I ² C1	1.71	
	I ² C2	1.68	
	WWDT	0.20	
	PWC	0.39	
	SCFG/CMP1	0.29	
	SPI1/I ² S1	2.03	
	USART1	2.12	
ADD2	TMR1	7.68	
APB2	TMR15	4.65	
	TMR16	3.19	
	TMR17	3.41	
	ADC1	5.17	



5.3.6 External clock source characteristics

High-speed external clock generated from a crystal / ceramic resonator

The high-speed external (HEXT) clock can be supplied with a 4 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in the table below. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 23. HEXT 4 ~ 25 MHz crystal characteristics (1)(2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fhext_in	Oscillator frequency	-	4	8	25	MHz
tsu(HEXT)(3)	Startup time	V _{DD} is stabilized	-	2	-	ms

- (1) Oscillator characteristics given by the crystal/ceramic resonator manufacturer.
- (2) Guaranteed by characterization results, not tested in production.
- (3) t_{SU(HEXT)} is the startup time measured from the moment HEXT is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

RF Bias Controlled gain

HEXT_OUT

RF C₁₂

Figure 13. HEXT typical application with an 8 MHz crystal

2022.6.6 39 Ver 2.01



High-speed external clock generated from an external source

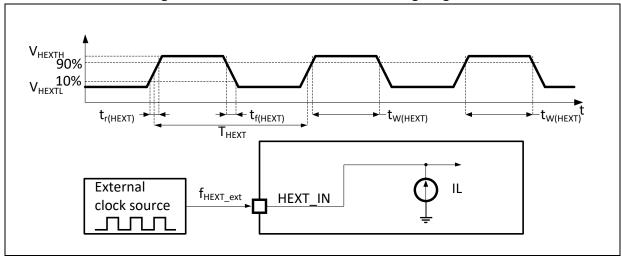
The characteristics given in the table below result from tests performed using a high-speed external clock source.

Table 24. HEXT external source characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fHEXT_ext	User external clock source frequency ⁽¹⁾		1	8	25	MHz
VHEXTH	HEXT_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
VHEXTL	HEXT_IN input pin low level voltage		Vss	-	0.3V _{DD}	V
tw(HEXT)	HEXT_IN high or low time ⁽¹⁾	-	5	-	-	
tr(HEXT)	HEXT_IN rise or fall time ⁽¹⁾		-	-	20	ns
Cin(HEXT)	HEXT_IN input capacitance ⁽¹⁾	-	-	5	-	pF
Duty(HEXT)	Duty cycle	-	45	-	55	%
IL	HEXT_IN input leakage current	Vss ≤ Vin ≤ Vdd	-	-	±1	μA

⁽¹⁾ Guaranteed by design, not tested in production.

Figure 14. HEXT external source AC timing diagram





Low-speed external clock generated from a crystal / ceramic resonator

The low-speed external (LEXT) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in the table below. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 25. LEXT 32.768 kHz crystal characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
tsu(LEXT)	Startup time	V _{DD} is stabilized	-	180	-	ms

⁽¹⁾ Oscillator characteristics are given by the crystal/ceramic resonator manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} , are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} .

Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$, where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

32.768 kHz crystal Bias Controlled gain

Figure 15. LEXT typical application with a 32.768 kHz crystal

Note:

No external resistor is required between LEXT_IN and LEXT_OUT, and it is also prohibited to add it.

2022.6.6 41 Ver 2.01

⁽²⁾ Guaranteed by characterization results, not tested in production.



Low-speed external clock generated from an external source

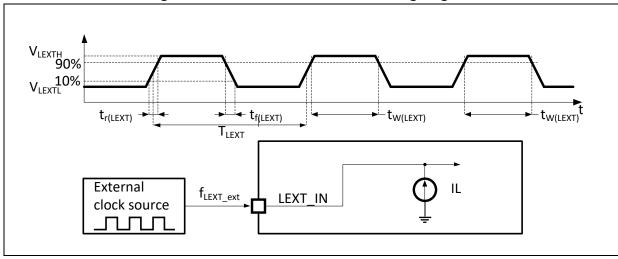
The characteristics given in the table below result from tests performed using a low-speed external clock source.

Table 26. LEXT external source characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fLEXT_ext	User external clock source frequency ⁽¹⁾		-	32.768	1000	kHz
VLEXTH	LEXT_IN input pin high level voltage		0.7V _{DD}	-	V _{DD}	V
VLEXTL	LEXT_IN input pin low level voltage		Vss	-	0.3V _{DD}	V
tw(LEXT)	LEXT_IN high or low time ⁽¹⁾	-	450	-	-	
tr(LEXT)	LEXT_IN rise or fall time ⁽¹⁾		-	-	50	ns
Cin(LEXT)	LEXT_IN input capacitance ⁽¹⁾	-	-	5	-	pF
Duty(LEXT)	Duty cycle	-	30	-	70	%
IL	LEXT_IN input leakage current	Vss ≤ Vin ≤ Vdd	-	-	±1	μA

⁽¹⁾ Guaranteed by design, not tested in production.

Figure 16. LEXT external source AC timing diagram



2022.6.6 42 Ver 2.01



5.3.7 Internal clock source characteristics

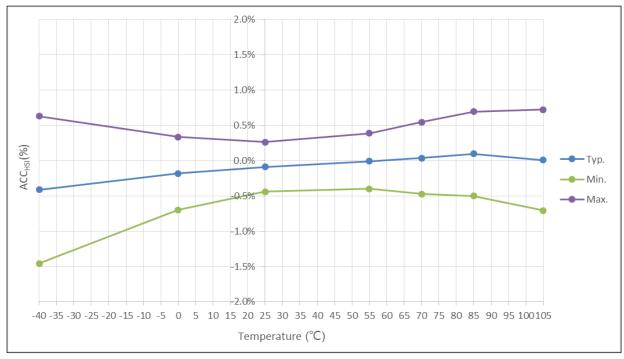
High-speed internal clock (HICK)

Table 27. HICK clock characteristics

Symbol	Parameter	C	Conditions		Тур	Max	Unit
fніск	Frequency	-		-	48	-	MHz
DuCy(HICK)	Duty cycle	-		45	-	55	%
		User-trimmed		-	-	1 ⁽¹⁾	%
400	Accuracy of the HICK		T _A = -40 ~ 105 °C	-2	-	1.5	%
ACCHICK	oscillator	Factory-	T _A = -40 ~ 85 °C	-2	-	1.2	%
		calibrated ⁽²⁾	T _A = 0 ~ 70 °C	-1.5	-	1.2	%
			T _A = 25 °C	-1	-	1	%
tsu(HICK) ⁽²⁾	HICK oscillator startup time		-	-	10	12	μs
IDD(HICK) ⁽²⁾	HICK oscillator power consumption		-	-	220	290	μΑ

⁽¹⁾ Guaranteed by design, not tested in production.

Figure 17. HICK clock accuracy vs. temperature



Low-speed internal clock (LICK)

Table 28. LICK clock characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
flick ⁽¹⁾	Frequency	-	25	35	45	kHz

⁽¹⁾ Guaranteed by characterization results, not tested in production.

2022.6.6 43 Ver 2.01

⁽²⁾ Guaranteed by characterization results, not tested in production.



5.3.8 PLL characteristics

Table 29. PLL characteristics

Symbol	Parameter	Min	Тур	Max ⁽¹⁾	Unit
6	PLL input clock ⁽²⁾	2	8	16	MHz
fpll_in	PLL input clock duty cycle	40	-	60	%
fpll_out	PLL multiplier output clock	16	-	120	MHz
tLOCK	PLL lock time	-	-	200	μs
Jitter	Cycle-to-cycle jitter	-	-	300	ps

⁽¹⁾ Guaranteed by characterization results, not tested in production.

5.3.9 Wakeup time from low-power mode

The wakeup times given in the table below is measured on a wakeup phase with the HICK. The clock source used to wake up the device depends from the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode.
- Deepsleep or Standby mode: the clock source is the HICK.

Table 30. Low-power mode wakeup time

Symbol	Parameter	Тур	Unit
twusleep	Wakeup from Sleep mode	3.3	μs
4	Wakeup from Deepsleep mode (regulator in normal mode)	380	
twustop	Wakeup from Deepsleep mode (regulator in low-power mode)	450	μs
twustdby	Wakeup from Standby mode	1250	μs

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

 EFT: A Burst of Fast Transient voltage (positive and negative) is applied to VDD and VSS through a coupling/decoupling network, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

Table 31. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
	Fast transient voltage burst limits to be applied through coupling/decoupling network conforms to IEC 61000-4-4 on	V _{DD} = 3.3 V, LQFP48, T _A = +25 °C, f _{HCLK} = 120 MHz, conforms to IEC 61000-4-4	
VEFT	V_{DD} and V_{SS} pins to induce a functional disturbance, V_{DD} and V_{SS} input has one 47 μF capacitor and each V_{DD} and V_{SS} pin pair $0.1 \mu F$.	V_{DD} = 3.3 V, LQFP48, T_A = +25 °C, f_{HCLK} = 72 MHz, conforms to IEC 61000-4-4	3/A (3.5 kV)

EMC characterization and optimization are performed at component level with a typical application environment. It should be noted that good EMC performance is highly dependent on the user application and the software in particular. Therefore it is recommended that the user applies EMC

2022.6.6 44 Ver 2.01

⁽²⁾ Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by fPLL_OUT.



software optimization and prequalification tests in relation with the EMC level requested for his application.

5.3.11 GPIO port characteristics

General input / output characteristics

All GPIOs are CMOS and TTL compliant.

Table 32. GPIO static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VIL	GPIO input low level voltage	-	-0.3	-	0.28 * V _{DD} + 0.1	V
	TC GPIO input high level voltage	-			V _{DD} + 0.3	
	FTa GPIO input high level voltage	Analog mode		-	V00+0.3	
Vih	FT GPIO input high level voltage	-	0.31 * V _{DD}			V
VIII	FTa GPIO input high level voltage	Input floating, input pull-up, or input pull-down mode	+ 0.8	-	5.5	v
\/ _i	Schmitt trigger veltage byeteresis(1)		200	-	-	mV
Vhys	Schmitt trigger voltage hysteresis ⁽¹⁾	-	5% Vdd	-	-	-
	(2)	Vss ≤ V _{IN} ≤ V _{DD} TC GPIO	-	-	±1	
llkg	Input leakage current ⁽²⁾	Vss ≤ V _{IN} ≤ 5.5V FT and FTa GPIO	-	-	±1	μΑ
Rpu	Weak pull-up equivalent resistor	VIN = Vss	65	80	130	kΩ
Rpd	Weak pull-down equivalent resistor (3)	VIN = VDD	65	70	130	kΩ
Cıo	GPIO pin capacitance	-	-	9	-	pF

⁽¹⁾ Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results, not tested in production.

All GPIOs are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters

Output driving current

In the user application, the number of GPIO pins which can drive current must be controlled to respect the absolute maximum rating defined in 5.2.1:

- The sum of the currents sourced by all GPIOs on V_{DD} plus the maximum Run consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating I_{VDD} (see *Table 7*).
- The sum of the currents sunk by all GPIOs on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS}, cannot not exceed the absolute maximum rating I_{VSS} (see *Table 7*).

2022.6.6 45 Ver 2.01

⁽²⁾ Leakage could be higher than max if negative current is injected on adjacent pins.

⁽³⁾ The pull-down resistor of BOOT0 exists permanently.



Output voltage levels

All GPIOs are CMOS and TTL compliant.

Table 33. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
Normal so	urcing/sinking strength				<u>'</u>
V _{OL} ⁽¹⁾	Output low level voltage	CMOS standard, I _{IO} = 4 mA	-	0.4	
VoH ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	V _{DD} -0.4	-	_ V
VoL ⁽¹⁾	Output low level voltage	TTL standard, I _{IO} = 2 mA	-	0.4	.,
V _{OH} ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	2.4	-	_ V
V _{OL} ⁽¹⁾	Output low level voltage	I _{IO} = 9 mA	-	1.3	.,
V _{OH} ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	V _{DD} -1.3	-	_ V
VoL ⁽¹⁾	Output low level voltage	I _{IO} = 2 mA	-	0.4	.,
V _{OH} ⁽¹⁾	Output high level voltage	2.4 V ≤ V _{DD} < 2.7 V	V _{DD} -0.4	-	_ V
Large sou	rcing/sinking strength		<u> </u>		•
Vol	Output low level voltage	CMOS standard, I _{IO} = 6 mA	-	0.4	
Vон	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	V _{DD} -0.4	-	_ V
VoL ⁽¹⁾	Output low level voltage	TTL standard, I _{IO} = 5 mA	-	0.4	V
V _{OH} ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	2.4	-	7 V
VoL ⁽¹⁾	Output low level voltage	I _{IO} = 18 mA	-	1.3	
V _{OH} ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	V _{DD} -1.3	-	_ V
V _{OL} ⁽¹⁾	Output low level voltage	I _{IO} = 4 mA	-	0.4	.,
V _{OH} ⁽¹⁾	Output high level voltage	2.4 V ≤ VDD < 2.7 V	V _{DD} -0.4	-	_ V
Maximum	sourcing/sinking strength	1			
Vol ⁽¹⁾	Output low level voltage	CMOS standard, I _{IO} = 15 mA	-	0.4	V
V _{OH} ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	V _{DD} -0.4	-	7 V
V _{OL} ⁽¹⁾	Output low level voltage	TTL standard, I _{IO} = 12 mA	-	0.4	
V _{OH} ⁽¹⁾	Output high level voltage	2.7 V ≤ V _{DD} ≤ 3.6 V	2.4	-	_ V
VoL ⁽¹⁾	Output low level voltage	I _{IO} = 12 mA	-	0.4	.,
V _{OH} ⁽¹⁾	Output high level voltage	2.4 V ≤ V _{DD} < 2.7 V	V _{DD} -0.4	-	_ v

⁽¹⁾ Guaranteed by characterization results, not tested in production.

Input AC characteristics

The definition and values of input AC characteristics are given as follows.

Table 34. Input AC characteristics

Symbol	Parameter	Min	Max	Unit
t EXINTpw	Pulse width of external signals detected by EXINT controller	10	-	ns



5.3.12 NRST pin characteristics

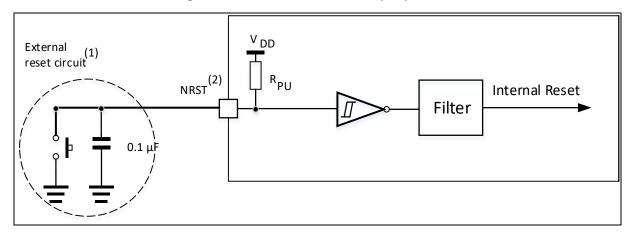
The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see the table below).

Table 35. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST input low level voltage	-	-0.3	-	0.72	V
VIH(NRST) ⁽¹⁾	NRST input high level voltage	-	2	-	V _{DD} + 0.3	V
V _{hys(NRST)}	NRST Schmitt trigger voltage hysteresis	-	-	400	-	mV
Rpu	Weak pull-up equivalent resistor	Vin = Vss	30	40	50	kΩ
V _{F(NRST)} ⁽¹⁾	NRST input filtered pulse	-	-	-	40	μs
V _{NF(NRST)} ⁽¹⁾	NRST input non-filtered pulse	-	80	-	-	μs

⁽¹⁾ Guaranteed by design, not tested in production.

Figure 18. Recommended NRST pin protection



- (1) The reset network protects the device against parasitic resets.
- (2) The user must ensure that the level on the NRST pin can go below the V_{IL(NRST)} max level specified in *Table 35*. Otherwise the reset will not be taken into account by the device.

5.3.13 TMR timer characteristics

The parameters given in the table below are guaranteed by design.

Table 36. TMR characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
	Timer recolution time	-	1	-	t TMRxCLK
tres(TMR)	Timer resolution time	f _{TMRxCLK} = 120 MHz	8.3	-	ns
f EXT	Timer external clock frequency on CH1 to CH4	-	0	f _{TMRxCLK} /2	MHz

2022.6.6 47 Ver 2.01



5.3.14 SPI / I²S characteristics

The parameters are listed in *Table 37* for SPI and in *Table 38* for I²S.

Table 37. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
fsck		Master mode	- 36		
(1/t _{c(SCK)}) ⁽¹⁾	SPI clock frequency ⁽²⁾⁽³⁾	Slave receive mode	-	36	MHz
(I/IC(SCK))		Slave transmit mode	-	32	
t _{su(CS)} (1)	CS setup time	Slave mode	4t _{PCLK}	-	ns
th(CS) ⁽¹⁾	CS hold time	Slave mode	2t _{PCLK} + 10	-	ns
tw(SCKH) ⁽¹⁾	CCV high and law time	Master mode, f _{PCLK} = 120 MHz,	24	01 4	20
tw(SCKL)(1)	SCK high and low time	prescaler factor = 4	2t _{PCLK} - 2	2t _{PCLK} + 1	ns
t _{su(MI)} ⁽¹⁾	Data input actus time	Master mode	4	-	20
t _{su(SI)} ⁽¹⁾	Data input setup time	Slave mode	5	-	ns
t _{h(MI)} ⁽¹⁾	Data in mut hald time	Master mode	4	-	
t _{h(SI)} ⁽¹⁾	- Data input hold time	Slave mode	5	-	ns
t _{a(SO)} (1)(4)	Data output access time	Slave mode , f _{PCLK} = 20 MHz	0	3t _{PCLK}	ns
t _{dis(SO)} (1)(5)	Data output disable time	Slave mode	0	18	ns
t _{v(SO)} ⁽¹⁾	Data output valid time	Slave mode (after enable edge)	-	22.5	ns
t _{v(MO)} ⁽¹⁾	Data output valid time	Master mode (after enable edge)	-	6	ns
t _{h(SO)} ⁽¹⁾	Data autout hald time	Slave mode (after enable edge)	11.5	-	
t _{h(MO)} ⁽¹⁾	- Data output hold time	Master mode (after enable edge)	2	-	ns

- (1) Guaranteed by characterization results, not tested in production.
- (2) The maximum SPI clock frequency in slave mode should not exceed fPCLK/2.
- (3) The maximum SPI clock frequency is highly related with devices and the PCB layout. For more details about the complete solution, please contact your local Artery sales representative.
- (4) Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
- (5) Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.



CS input $t_{c(SCK)}$ - t_{h(CS)} su(CS) -CPHA=0 t_{w(SCKH)} CPOL=0 t_{w(SCKL)} CPHA=0 -CPOL=1 $t_{v(SO)} \rightarrow \blacksquare$ t_{h(SO)} $t_{\text{a}(\text{SO})}$ t_{dis(SO)} MSB out LSB out MISO output t_{su(SI)} → $t_{h(SI)}$ MOSI input MSB in LSB in

Figure 19. SPI timing diagram – slave mode and CPHA = 0

Figure 20. SPI timing diagram – slave mode and CPHA = 1

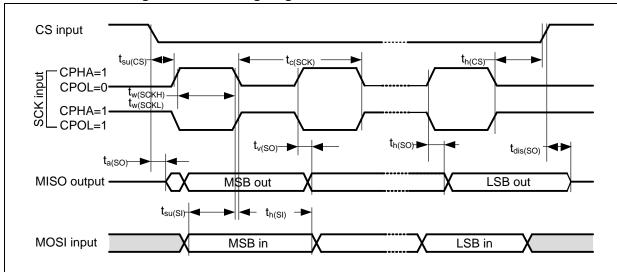


Figure 21. SPI timing diagram – master mode

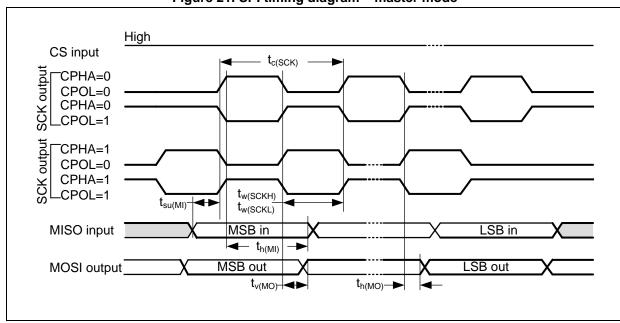


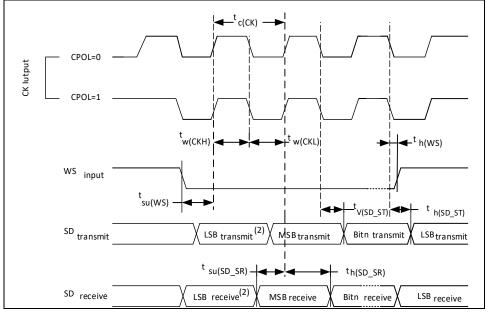


Table 38. I²S characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
tr(CK)	I ² S clock rise and fall time	Capacitive load: C = 15 pF	-	12	
t _{v(WS)} ⁽¹⁾	WS valid time	Master mode	2	-	
t _{h(WS)} ⁽¹⁾	WS hold time	Master mode	2	-	
tsu(WS) ⁽¹⁾	WS setup time	Slave mode	7	-	
t _{h(WS)} ⁽¹⁾	WS hold time	Slave mode	0	-	
tsu(SD_MR) ⁽¹⁾	Data input actum time	Master receiver	6	-	
tsu(SD_SR) ⁽¹⁾	Data input setup time	Slave receiver	2	-	ns
th(SD_MR)(1)(2)	Data input hald time	Master receiver	4	-	
t _{h(SD_SR)} (1)(2)	Data input hold time	Slave receiver	0.5	-	
t _{v(SD_ST)} (1)(2)	Data output valid time	Slave transmitter (after enable edge)	-	20	
th(SD_ST) ⁽¹⁾	Data output hold time	Slave transmitter (after enable edge)	13	-	
t _{v(SD_MT)} (1)(2)	Data output valid time	Master transmitter (after enable edge)	-	4	
th(SD_MT) ⁽¹⁾	Data output hold time	Master transmitter (after enable edge)	0	-	

⁽¹⁾ Guaranteed by design and/or characterization results, not tested in production.

Figure 22. I²S slave timing diagram (Philips protocol)



⁽¹⁾ LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

2022.6.6 50 Ver 2.01

⁽²⁾ Depends on fPCLK. For example, if fPCLK = 8 MHz, then tPCLK = 1/fPCLK = 125 ns.



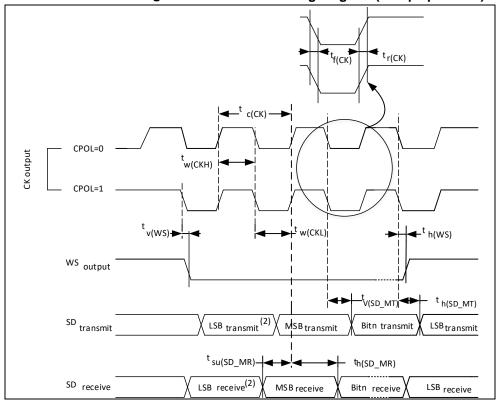


Figure 23. I²S master timing diagram (Philips protocol)

(1) LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

5.3.15 I²C interface characteristics

GPIO pins SDA and SCL have limitation as follows: they are not "true" open-drain. When configured as open-drain, the PMOS connected between the GPIO pin and V_{DD} is disabled, but is still present.

I²C bus interface can support standard mode (max. 100 kHz) and fast mode (max. 400 kHz). The I²C bus frequency can be increased up to 1 MHz. For more complete information, please contact your local Artery sales office for technical support.

2022.6.6 51 Ver 2.01



5.3.16 12-bit ADC characteristics

Unless otherwise specified, the parameters given in the table below are preliminary values derived from tests performed under ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 11*.

Note: It is recommended to perform a calibration after each power-up.

Table 39. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VDDA	Power supply	-	2.4	-	3.6	V
Idda	Current on the V _{DDA} input pin	-	-	480 ⁽¹⁾	560	μA
fadc	ADC clock frequency	-	0.6	-	28	MHz
fs ⁽²⁾	Sampling rate	-	0.05	-	2	MHz
f _{TRIG} (2)	External trigger	f _{ADC} = 28 MHz	-	-	1.65	MHz
ITRIG(=)	frequency	-	-	-	17	1/fadc
Vain	Conversion voltage range ⁽³⁾	-	0 (V _{REF} - tied to ground)	-	VREF+	٧
R _{AIN} ⁽²⁾	External input impedance	-	See Table 40 and Table 41			
C _{ADC} ⁽²⁾	Internal sample and hold capacitor	-	-	8.5	13	pF
t _{CAL} ⁽²⁾	Calibration time	f _{ADC} = 28 MHz	6.61			μs
(CAL ⁽⁻⁾	Calibration time	-	185			1/fadc
t _{latr} (2)	Trigger conversion	f _{ADC} = 28 MHz	-	-	71.4	μs
latr'⁻/	latency	-	-	-	2 ⁽⁴⁾	1/fadc
ts ⁽²⁾	Sampling time	f _{ADC} = 28 MHz	0.053	-	8.55	μs
is'-'	Sampling time	-	1.5	-	239.5	1/fadc
tstab ⁽²⁾	Power-on time	-	42			1/fadc
	Total conversion	f _{ADC} = 28 MHz	0.5	-	9	μs
t _{CONV} (2)	time(including sampling time)	-	14~252 (t _S for sampling approxim		successive	1/fadc

⁽¹⁾ Guaranteed by characterization results, not tested in production.

⁽²⁾ Guaranteed by design, not tested in production.

⁽³⁾ V_{REF+} can be internally connected to V_{DDA}, and V_{REF-} can be internally connected to V_{SSA}, depending on the package.

⁽⁴⁾ For external triggers, a delay of 1/f_{PCLK2} must be added to the latency specified in *Table 39*.



Table 40 and *Table 41* are used to determine the maximum external impedance allowed for an error below 1/4 of 1 LSB.

Table 40. R_{AIN} max for $f_{ADC} = 14$ MHz (1)

T _S (Cycle)	t _S (µs)	R _{AIN} max (kΩ)
1.5	0.11	0.35
7.5	0.54	3.9
13.5	0.96	7.4
28.5	2.04	16.3
41.5	2.96	24.0
55.5	3.96	32.3
71.5	5.11	41.8
239.5	17.11	50.0

⁽¹⁾ Guaranteed by design.

Table 41. R_{AIN} max for f_{ADC} = 28 MHz (1)

Ts (Cycle)	ts (µ s)	R _{AIN} max (kΩ)
1.5	0.05	0.1
7.5	0.27	1.6
13.5	0.48	3.4
28.5	1.02	7.9
41.5	1.48	11.7
55.5	1.98	15.9
71.5	2.55	20.6
239.5	8.55	50.0

⁽¹⁾ Guaranteed by design.

2022.6.6 53 Ver 2.01

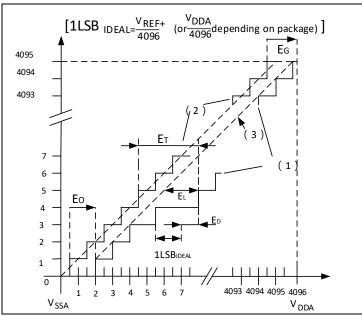


Table 42. ADC accuracy (1)

Symbol	Parameter	Test Conditions	Typ ⁽²⁾	Max ⁽²⁾	Unit
ET	Total unadjusted error		+2	+3.5	
EO	Offset error	f _{PCLK2} = 56 MHz,	+1	+2.5	
EG	Gain error	$f_{ADC} = 28 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega,$	+1.5	+3	LSB
ED	Differential linearity error	V _{DDA} = 3.0~3.6 V, T _A = 25 °C	±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	
ET	Total unadjusted error		±2	+4	
EO	Offset error	f _{PCLK2} = 56 MHz,	+1	+3	
EG	Gain error	$f_{ADC} = 28 \text{ MHz}, R_{AIN} < 10 \text{ k}\Omega,$	+1.5	+3.5	LSB
ED	Differential linearity error	V _{DDA} = 2.4~3.6 V	±0.6	+1.5/-1	
EL	Integral linearity error		±1	±2.5	

- (1) ADC DC accuracy values are measured after internal calibration.
- (2) Guaranteed by characterization results, not tested in production.

Figure 24. ADC accuracy characteristics

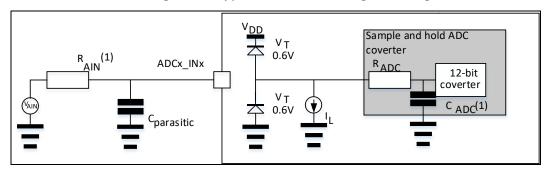


- (1) Example of an actual transfer curve.
- (2) Ideal transfer curve.
- (3) End point correlation line.
- (4) ET = Maximum deviation between the actual and the ideal transfer curves.
 - EO = Deviation between the first actual transition and the first ideal one.
 - EG = Deviation between the last ideal transition and the last actual one.
 - ED = Maximum deviation between actual steps and the ideal one.
 - EL = Maximum deviation between any actual transition and the end point correlation line.

2022.6.6 54 Ver 2.01



Figure 25. Typical connection diagram using the ADC



- (1) Refer to Table 39 for the values of Rain and Cadc.
- (2) C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C_{parasitic} value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 8*. The 100 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

5.3.17 Internal reference voltage (VINTRV) characteristics

Table 43. Internal reference voltage characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VINTRV	Internal reference voltage	-	1.17	1.20	1.23	V
T _{Coeff} ⁽¹⁾	Temperature coefficient	-	-	50	100	ppm/°C
T _{S_VINTRV}	ADC sampling time when reading the internal reference voltage	-	5.1	-	-	μs

⁽¹⁾ Guaranteed by design, not tested in production.

5.3.18 Temperature sensor (V_{TS}) characteristics

Table 44. Temperature sensor characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _L (1)	V _{TS} linearity with temperature	T _A = -20 ~ 85 °C	-	±1	±1.5	∘C
I L(··/		T _A = -40 ~ 105 °C	-	-	±2	
Avg_Slope(1)(2)	Average slope		-4.17	-4.30	-4.44	mV/ºC
V ₂₅ ⁽¹⁾⁽²⁾	Voltage at T=25 °C		1.22	1.28	1.34	V
tstart ⁽³⁾	Setup time		-	-	100	μs
T (3)	ADC sampling time when			0.6	17.1	
Ts_temp ⁽³⁾	reading the temperature		-	8.6	17.1	μs

⁽¹⁾ Guaranteed by characterization results, not tested in production.

Obtain the temperature using the following formula:

Temperature (°C) = $\{(V_{25} - V_{TS}) / Avg_Slope\} + 25$ Where,

V₂₅ = V_{TS} value for 25 °C

Avg_Slope = average slope for curve between temperature vs. Vsense (given in mV/°C)

2022.6.6 55 Ver 2.01

⁽²⁾ The temperature sensor output voltage changes linearly with temperature. The offset of this line varies from chip to chip due to process variation (up to 50 °C from one chip to another). The internal temperature sensor is more suited to applications that detect temperature variations instead of absolute temperatures. If accurate temperature readings are needed, an external temperature sensor part should be used.

⁽³⁾ Guaranteed by characterization design, not tested in production.



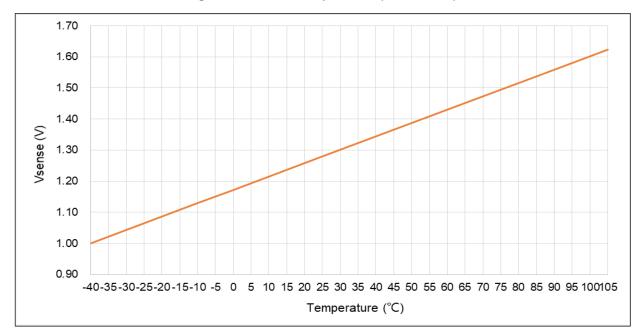


Figure 26. V_{TS} vs. temperature (ideal curve)

5.3.19 Comparator (CMP) characteristics

Table 45. Comparator characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
Vdda	Power supply voltage	-	2.4	-	3.6	V
V _{IN}	Input voltage range	-	0	-	Vdda	V
		High speed mode	-	1.0	3.5	
	Otantum tima	Medium speed mode	-	2.8	5	Ī
tstart	Startup time	Low power mode	-	8	13	μs
		Ultra low power mode	-	12	18	
	Propagation delay for 200 mV step with 100 mV overdrive High speed mode Medium speed mode Low power mode Ultra low power mode	High speed mode	-	40	100	
		Medium speed mode	-	240	320	ns
t⊳		Low power mode	-	500	820	
		Ultra low power mode -	-	800	1800	
V _{offset}	Offset voltage	-	-	±4	±15	mV
		No hysteresis	-	0	1	
	I hasta wa sia	Low hysteresis	5	8	17	
V_{hys}	Hysteresis	Medium hysteresis	10	18	37	mV
		High hysteresis	18	38	70	
		High speed mode	-	40	61	
	Owner to a V in the time	Medium speed mode	-	9.7	13.9	- μA -
IDDA	Current on V _{DDA} input pin	Low power mode	-	3.2	4.7	
		Ultra low power mode	-	1.9	2.8	

⁽¹⁾ Guaranteed by design, not tested in production.



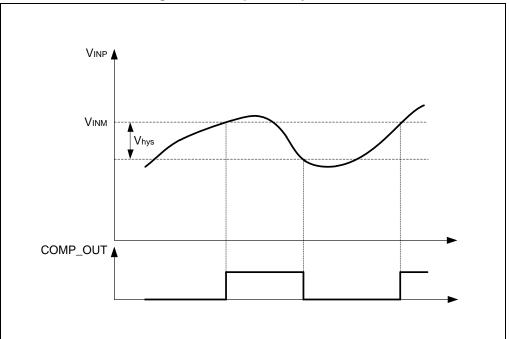


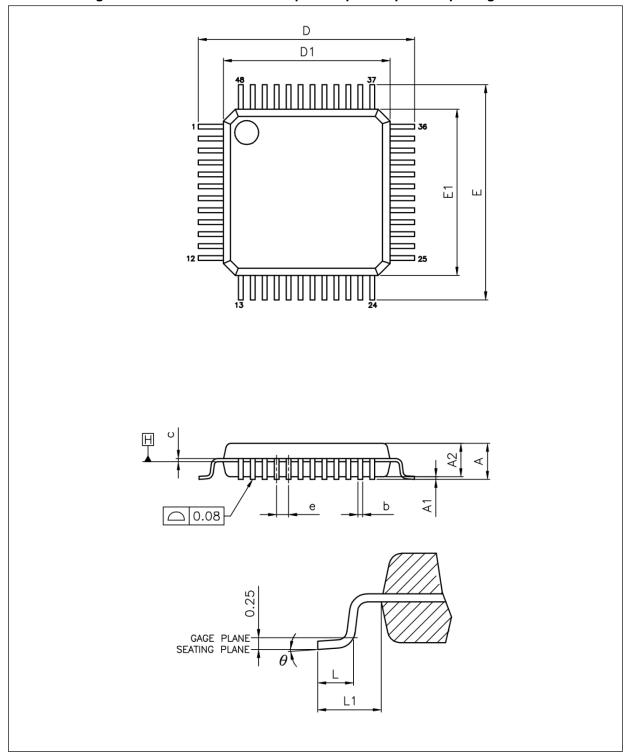
Figure 27. Comparator hysteresis



6 Package information

6.1 LQFP48 – 7 x 7 mm

Figure 28. LQFP48 – 7 x 7 mm 48 pin low-profile quad flat package outline





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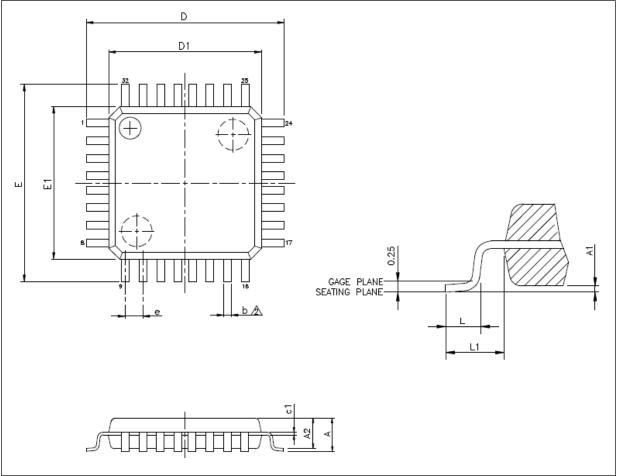
Table 46. LQFP48 – 7 x 7 mm 48 pin low-profile quad flat package mechanical data

Oh. a l	Millimeters		
Symbol	Min	Тур	Max
А	-	-	1.60
A1	0.05	-	0.15
A2	1.35	1.40	1.45
b	0.17	0.22	0.27
С	0.09	-	0.20
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
E	8.80	9.00	9.20
E1	6.90	7.00	7.10
е		0.50 BSC.	
Θ	0°	3.5°	7°
L	0.45	0.60	0.75
L1		1.00 REF.	



6.2 LQFP32 - 7 x 7 mm

Figure 29. LQFP32 – 7 x 7 mm 32 pin low-profile quad flat package outline





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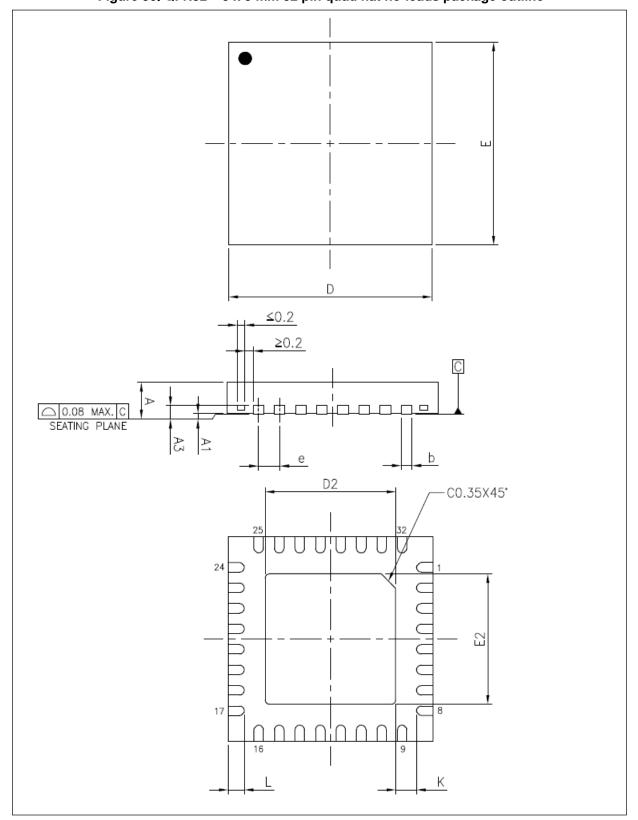
Table 47. LQFP32 – 7 x 7 mm 32 pin low-profile quad flat package mechanical data

O. make at	Millimeters		
Symbol	Min	Тур	Max
А	-	-	1.60
A1	0.05	-	0.15
A2	1.35	-	1.45
b	0.30	-	0.45
С	0.09	-	0.16
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
E	8.80	9.00	9.20
E1	6.90	7.00	7.10
е		0.80 BSC.	
L	0.45	-	0.75
L1		1.00 REF.	



6.3 QFN32 – 5 x 5 mm

Figure 30. QFN32 – 5 x 5 mm 32 pin quad flat no-leads package outline





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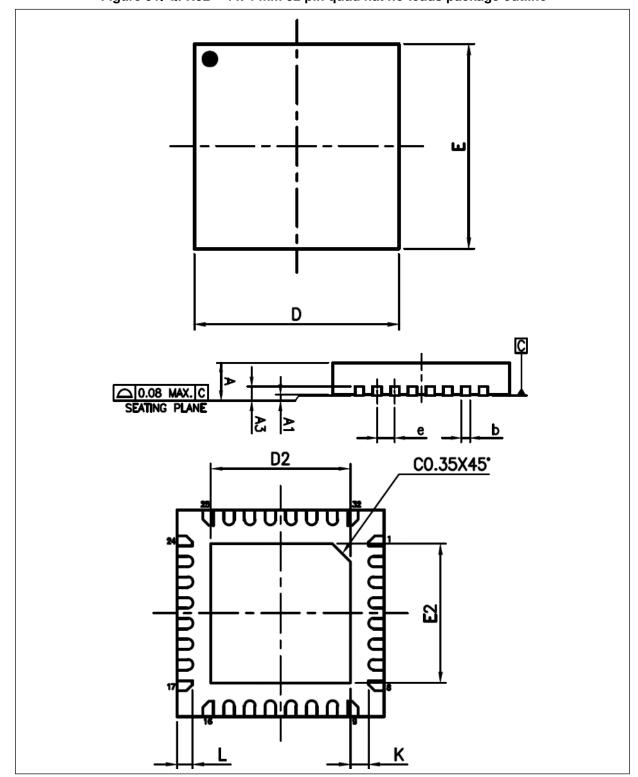
Table 48. QFN32 – 5 x 5 mm 32 pin quad flat no-leads package mechanical data

O. mahad	Millimeters		
Symbol	Min	Тур	Max
А	0.70	0.75	0.80
A1	0.00	0.02	0.05
A3	0.203 REF.		
b	0.18	0.25	0.30
D	4.90	5.00	5.10
D2	3.20	3.25	3.30
E	4.90	5.00	5.10
E2	3.20	3.25	3.30
е	0.50 BSC.		
K	0.20	-	-
L	0.35	0.40	0.45



6.4 QFN32 – 4 x 4 mm

Figure 31. QFN32 – 4 x 4 mm 32 pin quad flat no-leads package outline





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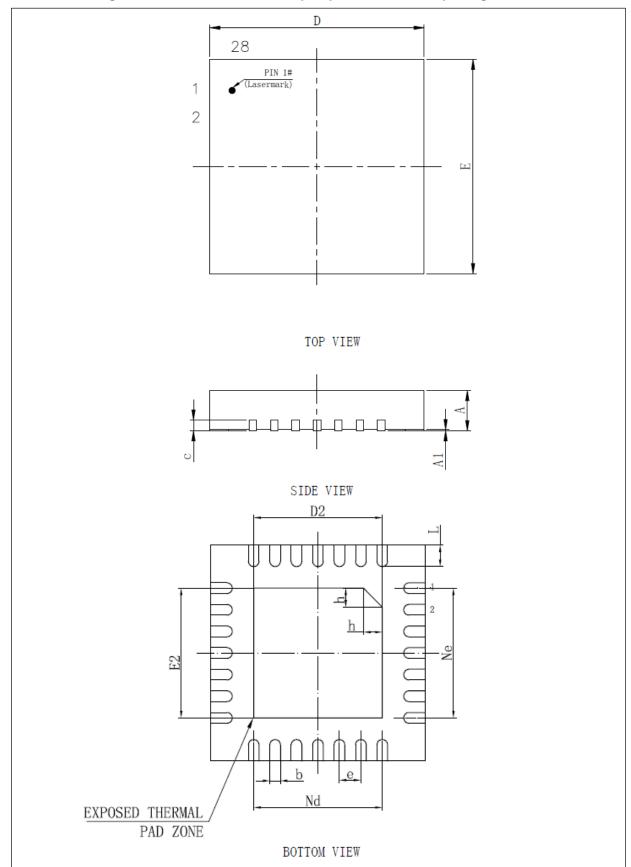
Table 49. QFN32 – 4 x 4 mm 32 pin quad flat no-leads package mechanical data

Comple at	Millimeters		
Symbol	Min	Тур	Max
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
A3	0.203 REF.		
b	0.15	0.20	0.25
D	3.90	4.00	4.10
D2	2.65	2.70	2.75
E	3.90	4.00	4.10
E2	2.65	2.70	2.75
е	0.40 BSC.		
K	0.20	-	-
L	0.25	0.30	0.35



6.5 QFN28 – 4 x 4 mm

Figure 32. QFN28 - 4 x 4 mm 28 pin quad flat no-leads package outline





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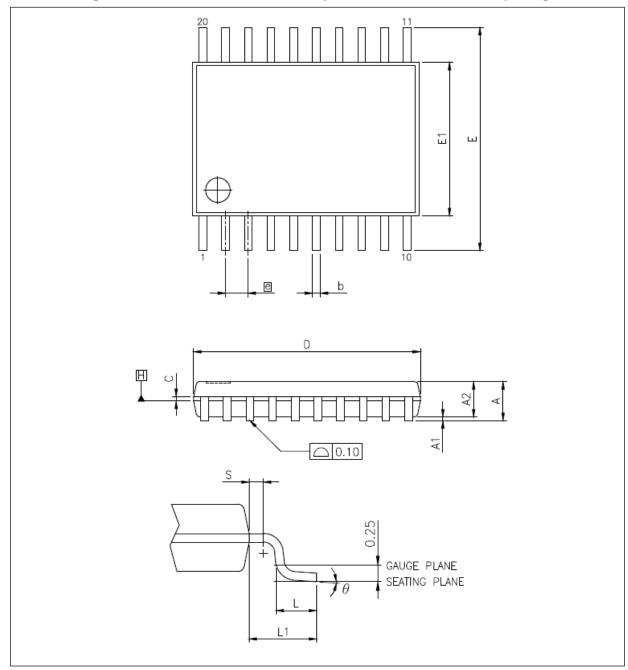
Table 50. QFN28 – 4 x 4 mm 28 pin quad flat no-leads package mechanical data

Ol	Millimeters		
Symbol	Min	Тур	Max
А	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.15	0.20	0.25
С	0.18	0.20	0.25
D	3.90	4.00	4.10
D2	2.30	2.40	2.50
Nd	2.40 BSC.		
E	3.90	4.00	4.10
E2	2.30	2.40	2.50
Ne		2.40 BSC.	
е	0.40 BSC.		
L	0.35	0.40	0.45
h	0.30	0.35	0.40



6.6 TSSOP20 - 6.5 x 4.4 mm

Figure 33. TSSOP20 – 6.5 x 4.4 mm 20 pin thin shrink small outline package





AT32F421 Series Datasheet

Table 51. TSSOP20 - 6.5 x 4.4 mm 20 pin thin shrink small outline package mechanical data

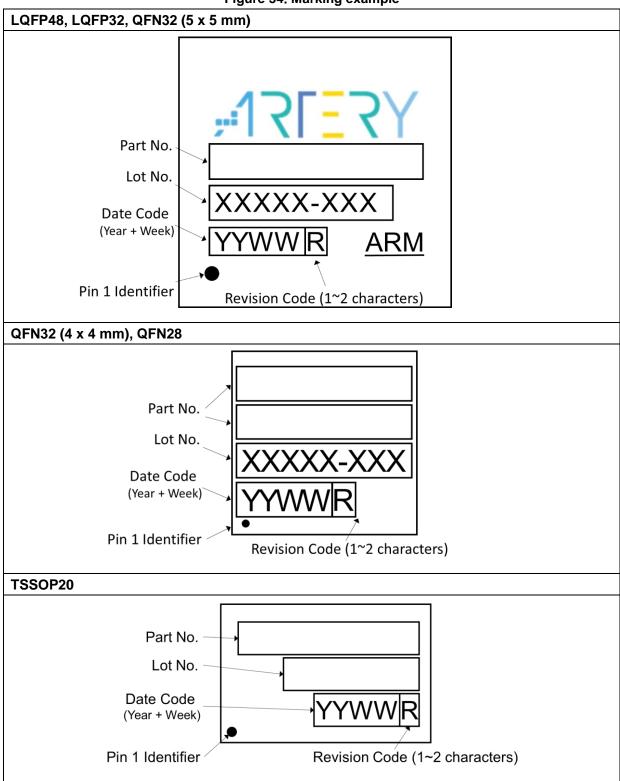
Oh al	Millimeters		
Symbol	Min	Тур	Max
Α	-	-	1.20
A1	0.05	-	0.15
A2	0.80	1.00	1.05
b	0.19	-	0.30
С	0.09	-	0.20
D	6.40	6.50	6.60
E1	4.30	4.40	4.50
E	6.20	6.40	6.60
е	0.65 BSC.		
L1		1.00 REF.	
L	0.50	0.60	0.75
S	0.20	-	-
Θ	0°	-	8°



6.7 Device marking

Artery devices may have the following markings, depending on the types of packages.

Figure 34. Marking example



(1) Not in scale.



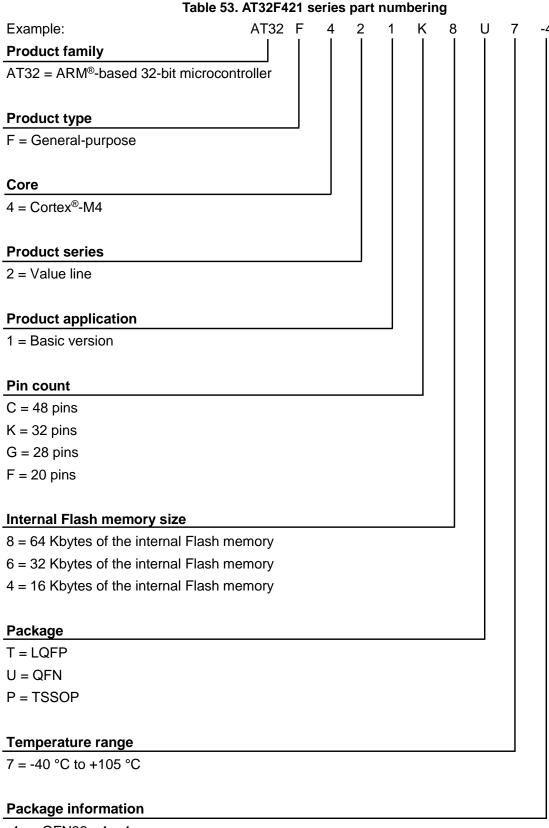
6.8 Thermal characteristics

Table 52. Package thermal characteristics

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient – LQFP48 – 7 x 7 mm	87.0	
	Thermal resistance junction-ambient – LQFP32 – 7 x 7 mm	82.4	
Θ _{JA}	Thermal resistance junction-ambient – QFN32 – 5 x 5 mm	39.8	°C/W
OJA	Thermal resistance junction-ambient – QFN32 – 4 x 4 mm	44.8	C/VV
	Thermal resistance junction-ambient – QFN28 – 4 x 4 mm	44.8	
	Thermal resistance junction-ambient – TSSOP20 – 6.5 x 4.4 mm	103.0	



7 Part numbering



 $-4 = QFN32 - 4 \times 4 mm$

None = Other packages

For a list of available options (speed, package, etc.) or for more information concerning this device, please contact your local Artery sales office.



8 Document revision history

Table 54. Document revision history

Date	Version	Change
2020.8.17	1.00	Initial release
		1. The maximum frequency of APB1 and APB2 is updated to 120 MHz in Figure
		1, Table 11 and Table 22.
2020.9.16	1.01	2. Modified the conditions and maximum values of SPI clock frequencies in <i>Table</i>
2020.9.10	1.01	37.
		3. Added EFT test result 3/A (2 kV) in Table 31.
		4. Added note (4) in <i>Table 5</i> .
		1. Updated comparator V _{offset} data in <i>Table 45</i> .
2021.7.1	1.02	2. Updated temperature sensor T _L data in <i>Table 44</i> .
		3. Modified LQFP48 package data.
		Updated document architecture and related descriptions.
2022.1.7	2.00	2. Modified comparator V _{offset} data in <i>Table 45</i> .
		3. Modified QFN28 package data.
		1. Added note (4) in Table 21.
2022.6.6	2.01	2. Added the minimum and maximum values of D, D1, E and E1 for each
		package.



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